

Institute of Mechanics, Materials and Civil Engineering

- & Research Center on Architectured and Composite Materials (ARCOMAT)
- & Research center in micro and nanoscopic materials and electronic devices (CERMIN)

Damage and fracture in thin films and other nano-objects

Est ce vraiment assez pour 40'?

T. Pardoen

Colloque MECAMAT Rupture des Matériaux et Structures 21-25 janvier, Aussois, France











Fracture of thin films and coating dictates the reliability of a variety of modern technologies

Flexible electronics

Zeng. Adv Mater(2014)

Nomura, Kenji et al. Nature (2004).

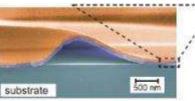
Philips' fluid' smartphone S. Coyle. MRS Bull (2007)

Thin functional coatings

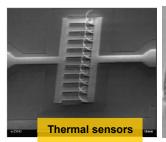
on glass, steel, Al, etc ... must resist:

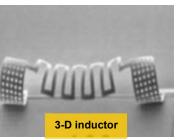
- thermomech. loadings
- forming operations after deposition
- impact
- scratch and wear

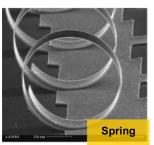




Mems and Nems







Micro and nano-electronics

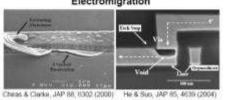
Fracture due to ratcheting

"Mud cracking" in BCB

Delamination and fracture of dielectrics

Lin & Vlassak, unpublished (2003)

Electromigration



Courtesy of J. Vlassak



1. Introduction

2. Fracture of thin films on substrates

- test methods and extraction of G
- example 1 : CrN on polymer (indentation)
- example 2 : SiN on polymer (subcritical crack growth)
- example 3 : Au on polymer (for flexible electronics)

3. Fracture of freestanding films

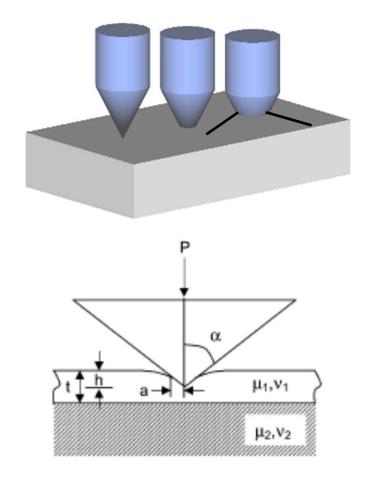
- test methods for measuring the fracture strength & strain
- fracture strength of brittle films (case of PolySi)
- fracture strain of ductile films (case of Al)
- fracture toughness

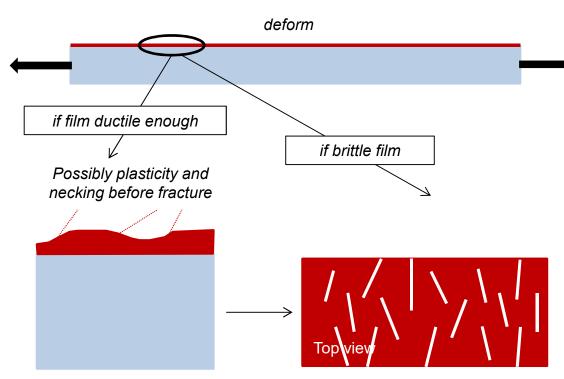


Approach 1: Thin films on substrate

Nanoindentation

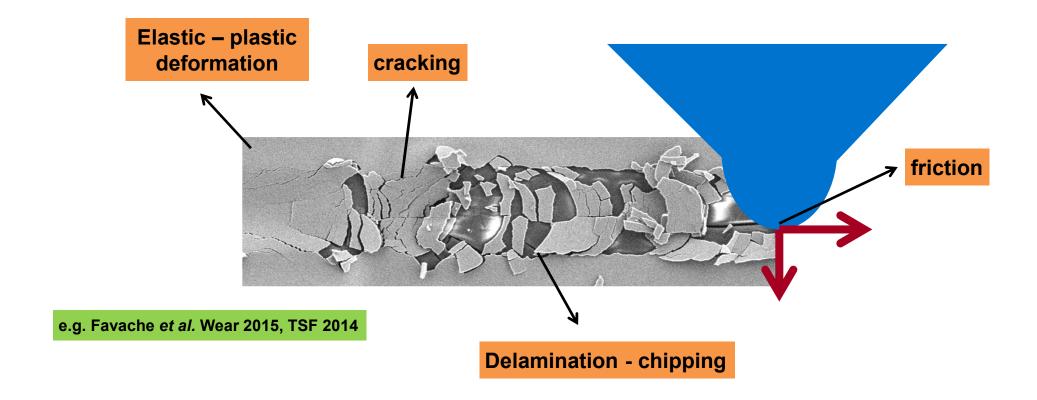
Tensile testing on elastomer







scratch

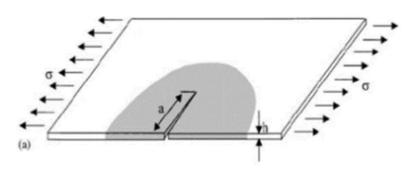


and many others: thermal loading, bending, etc



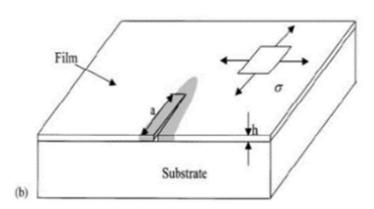
Basic expression of energy release rate for thin film (on substrate) fracture and delamination

Holding the plates at the loading grips fixed (du=0)



$$G = \frac{\partial W_{extForces}}{\partial A} - \frac{\partial W_e}{\partial A} = -\frac{\partial W_e}{\partial A}$$

$$\begin{cases} \Delta W_e = -Z\left(\frac{\alpha, \beta, \text{geometry}}{2E}\right) \frac{\sigma^2}{2E} a^2 h \\ G = -\frac{\partial W_e}{\partial A} = -\frac{1}{h} \frac{\Delta W_e}{\Delta a} = Z \frac{\sigma^2}{E} a \end{cases}$$



$$\begin{cases} \Delta W_e = -Z\left(\frac{\alpha,\beta,\text{geometry}}{2E}\right) \frac{\sigma^2}{2E} ah^2 \\ G = -\frac{\partial W_e}{\partial A} = -\frac{1}{h} \frac{\Delta W_e}{\Delta a} = Z \frac{\sigma^2}{E} h \end{cases}$$

G independent of a for films on substrate

$$G = Z \begin{pmatrix} \alpha, \beta, \sigma_{Y_S}, \text{ crack path, geometry} \\ \text{plasticity, viscoelasticity} \end{pmatrix} \frac{\sigma_R^2 h}{E_f}$$



General relationship for thin film (on substrate) fracture and delamination under tensile loading

$$G = Z(\alpha, \beta, \text{crack path, geometry}) \frac{\sigma_R^2 h}{E}$$



Surface Crack

Z = 3.951

Z here for no elastic mismatch and infinitely thick substrate (+ remember, G_c also depends on α and β through ψ)



Channeling

Z = 1.976



Spalling

Z = 0.343



Substrate Damage

Z = 3.951



Debond $Z = \begin{cases}
1.028 \text{ (initiation)} \\
0.5 \text{ (steady - state)}
\end{cases}$



Example 1: cracking resistance of CrN films on polymer

(as representative of many hard brittle coatings on softer substrates)



System of interest



Contents lists available at ScienceDirect

Thin Solid Films

journal homepage: www.elsevier.com/locate/tsf

Fracture toughness measurement of ultra-thin hard films deposited on a polymer interlayer

Audrey Favache ^{a,*}, Laure Libralesso ^b, Pascal J. Jacques ^a, Jean-Pierre Raskin ^c, Christian Bailly ^d, Bernard Nysten ^d, Thomas Pardoen ^a

1 to 20 μm polymer

Steel plate

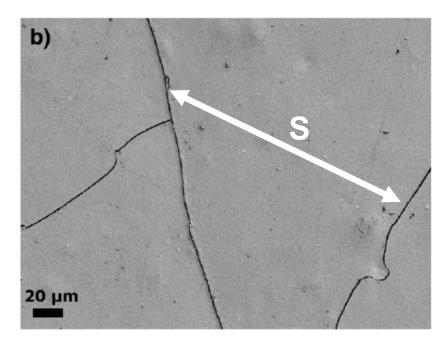
or

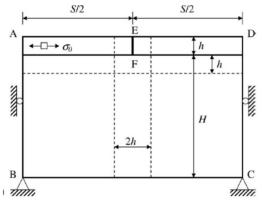
100 nm CrN (PVD)

Steel plate



Observation of channel cracks upon deposition

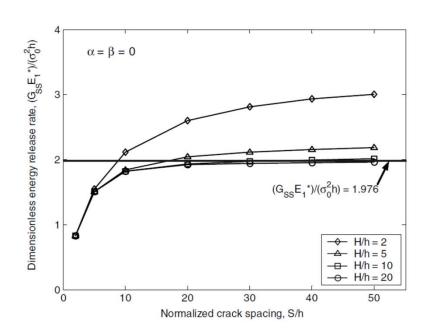




$$G = Z \begin{pmatrix} \alpha_{(polymer)}, \beta_{(polymer)}, \\ \text{channel crack spacing} \end{pmatrix} \frac{\sigma_R^2 h}{E_f}$$

$$\alpha = \frac{E_f^* - E_s^*}{E_f^* + E_s^*} \text{ and } \beta = \frac{\mu_f (1 - 2\nu_s) - \mu_s (1 - 2\nu_f)}{2\mu_f (1 - \nu_s) + 2\mu_s (1 - \nu_f)}$$

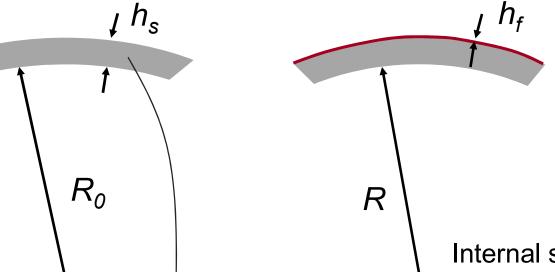
weak effect for channel cracks if $\alpha > 0$





Extraction of internal stress with Stoney method

on Si wafer !!



on Si wafer !!

Internal stress slightly varies with polymer interlayer: from 830 to 930 MPa

$$\sigma_R \approx -\frac{1}{6} \frac{E_s}{\left(1 - \nu_s\right)} \frac{h_s^2}{h_f} \left(\frac{1}{R} - \frac{1}{R_0}\right)$$

(we take the one from a system showing no cracking – CrN on steel : **910 MPa**)



Observation of channel cracks upon deposition

$$G = Z(\alpha_{polymer}, \beta_{polymer}, channelcrack) \frac{\sigma_R^2 h}{E_f}$$

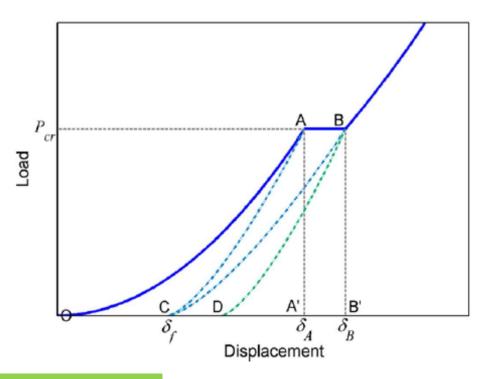
Crack propagation energy release rate calculated from initial cracking. For cracked samples $G = G_{Ic}$ (in italic). The 95% confidence interval given in brackets is calculated from the error on the internal stress and on the substrate modulus.

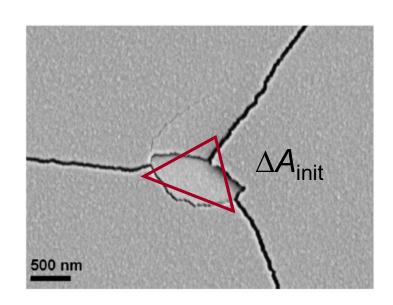
Sample	α	Crack spacing S [$Z \qquad G \left[J/m^2 \right]$	
CrN-steel	0.01	Uncracked	2.0	0.7 [0.6, 0.8]
CrN-Si	0.14	Uncracked	2.2	0.8 [0.7, 0.9]
CrN-P1-steel	0.95	48 ± 10	14	4.9 [4.4, 6.5]
CrN-P1-Si	0.95	60 ± 15	14	4.9 [4.4, 6.5]
CrN-P2-steel	0.99	100 ± 20	39	13.2 [11.8, 14.6]
CrN-P3-steel	0.97	67 ± 10	22	7.4 [6.6, 8.6]
CrN-P4-steel	0.98	56 ± 10	29	9.7 [8.5, 11.2]
CrN-PI-Si	0.98	18000	28	9.7 [8.7, 10.8]

Note: polymer interlayer favours cracking!



Indentation based cracking (more complex than for bulk!)





Chen and Bull, TSF 2009

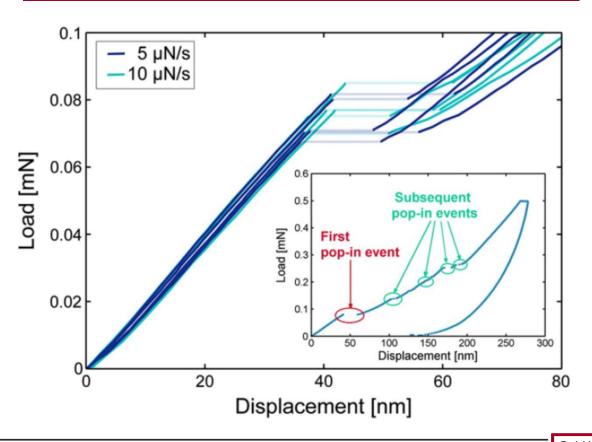
Lower bound Upper bound
$$U_1 = \int_{\delta_f}^{\delta_A} P_{cr} \left(\frac{x - \delta_f}{\delta_A - \delta_f} \right)^m dx + P_{cr} (\delta_B - \delta_A) \text{ and } U_2 = \int_{\delta_f}^{\delta_B} P_{cr} \left(\frac{x - \delta_f}{\delta_B - \delta_f} \right)^n dx.$$

$$G = \Delta U / \Delta A$$

Note: cracking observed only with polymer interlayer!



Indentation based cracking



Sample	α	Crack spacing S [µm]	Z	(* 1/111 T	G (J/m ²) from indent
CrN-steel	0.01	Uncracked	2.0	0.7 [0.6, 0.8]	
CrN-Si	0.14	Uncracked	2.2	0.8 [0.7, 0.9]	
CrN-P1-steel	0.95	48 ± 10	14	4.9 [4.4, 6.5]	
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CrN-P2-steel	0.99	100 ± 20	39	13.2 [11.8, 14.6]	
CrN-P3-steel	0.97	67 ± 10	22	7.4 [6.6, 8.6]	7.1 ± 5.7
CrN-P4-steel	0.98	56 ± 10	29	9.7 [8.5, 11.2]	
CrN-PI-Si	0.98	18000	28	9.7 [8.7, 10.8]	14.7 ± 10



Example 2 : cracking resistance of SiN films on polymer

(as representative of many hard brittle coatings on softer substrates)



www.acsami.org

Environmentally Assisted Cracking in Silicon Nitride Barrier Films on Poly(ethylene terephthalate) Substrates

Kyungjin Kim, Hao Luo, Ankit K. Singh, Ting Zhu, Samuel Graham,* and Olivier N. Pierron*

George W. Woodruff School of Mechanical Engineering, Georgia Institute of Technology, Atlanta, Georgia 30332, United States



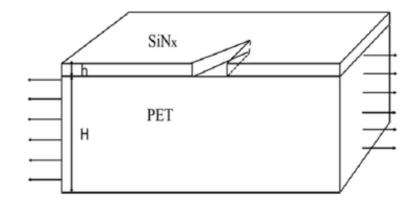
© 2016 American Chemical Society

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DOI: 10.1021/acsami.6b06417 ACS Appl. Mater. Interfaces 2016, 8, 27169–27178

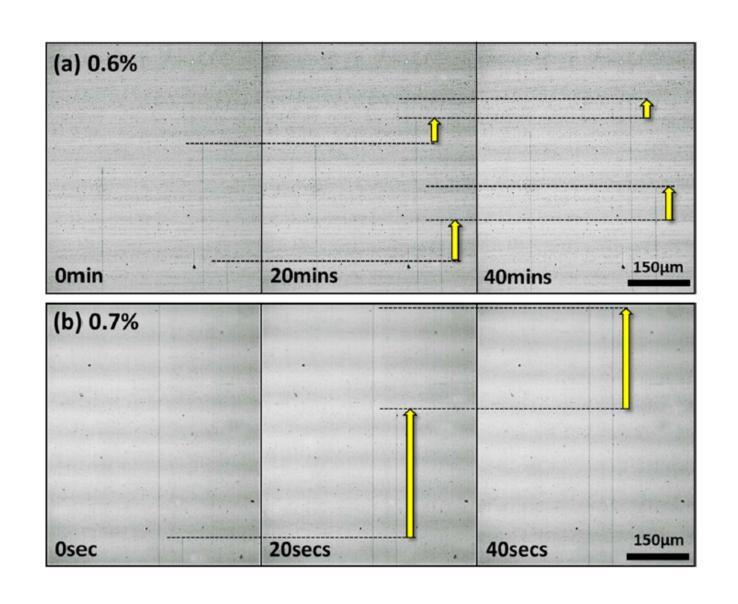
15 to 250 nm SiN (PECVD)

125 μm PET polymer



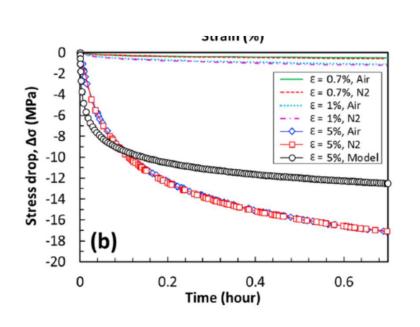


Crack propagation measurement under constant strain and controlled humidity

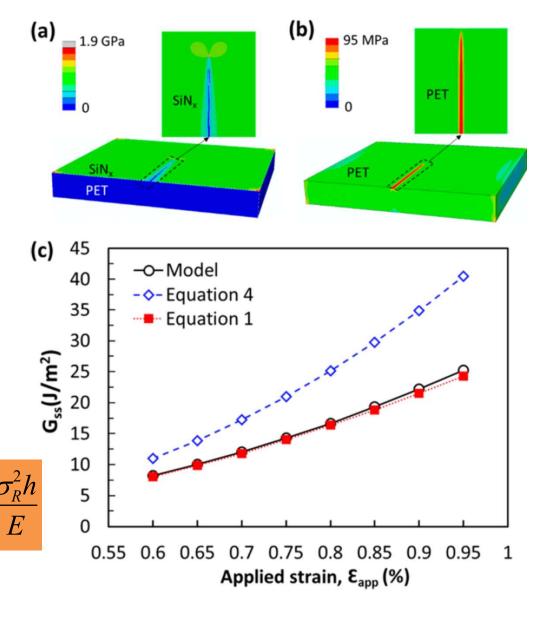




But very difficult to deconvolute relaxation effects associated to the PET substrate

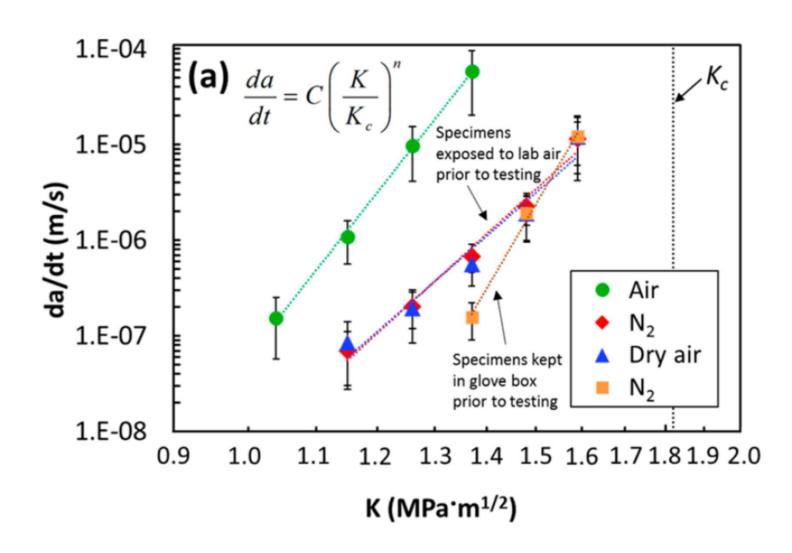


 $G = Z \begin{pmatrix} \alpha, \beta, \sigma_{\gamma_s}, \text{ crack path, plasticity} \\ \text{geometry, viscoelasticity} \end{pmatrix}$





Superb results



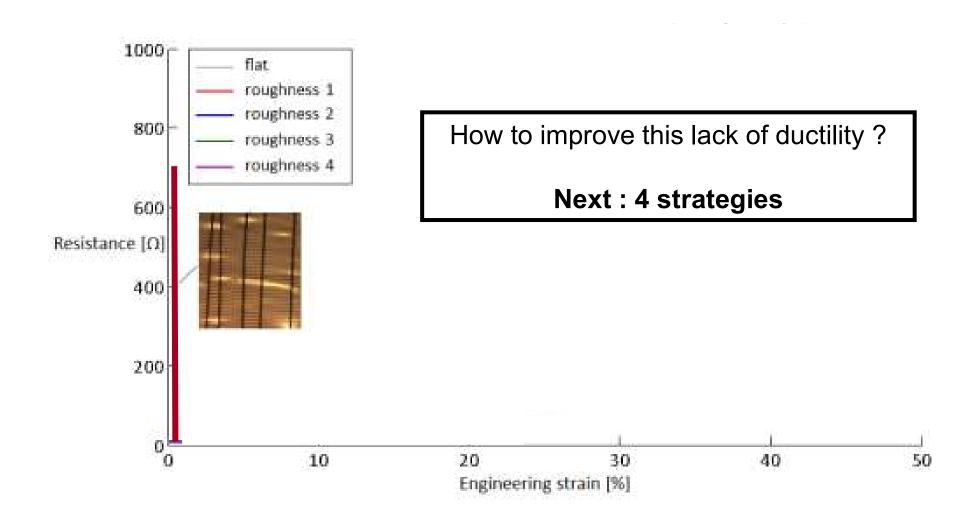


Example 3 : cracking resistance of Au films on polymer

(as representative of metal on polymer flexible electronics type devices)



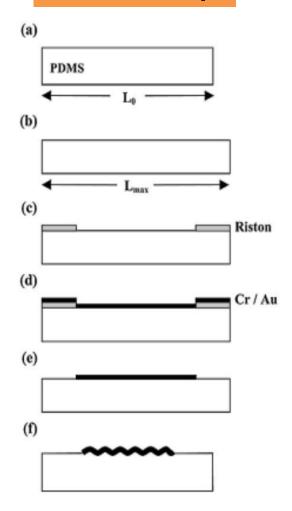
Thin Au films are not ductile (fracture strain below 1 or 2 %)





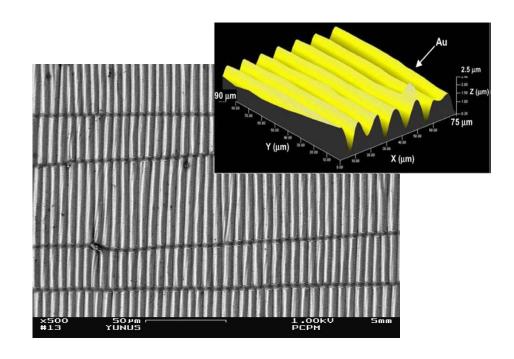
First ductilization principle: wrinkling patterns

Basic concept



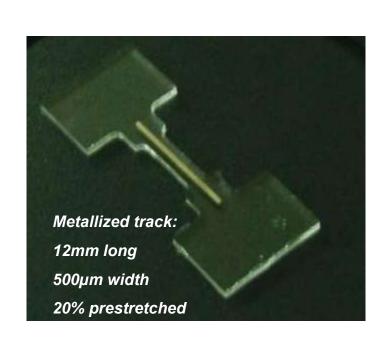
5 to 30% of prestretch5 nm of Cr adhesion layer100 nm gold evaporatedUpon release, wavelet morphology

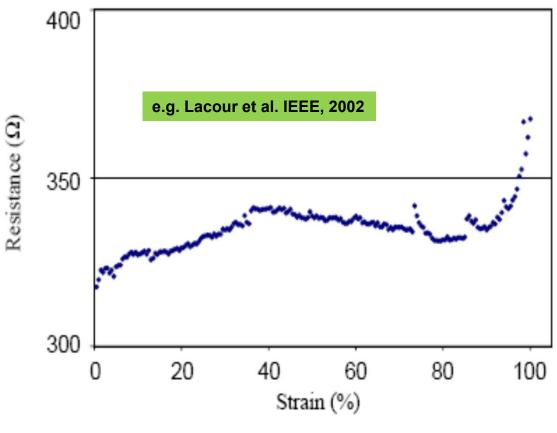
e.g. Lacour et al. IEEE, 2002





High stretchability without loss of electrical conductivity under monotonous and cyclic loadings







Basic buckling analysis

Wrinkling allows releasing the large compressive stresses built in the metal layer upon unloading

Simple structural mechanics analysis (see e.g. Allen, 1969) allows predicting, for infinitely thick substrates the wavelength and critical stress

$$\lambda \approx 4.4 t_{film} \left(\frac{E_{film}}{E_{sub}} \right)^{1/3}$$

$$\sigma_{crit} \approx 0.5 (E_{film})^{1/3} (E_{sub})^{2/3}$$

For gold on PDMS,

 $\lambda \approx 60 t_{film}$

 $\sigma_{crit} \approx 200 \text{MPa}$



Second ductilization principles: 2D in plane or 3D out of plane structures

+ Contact and integration

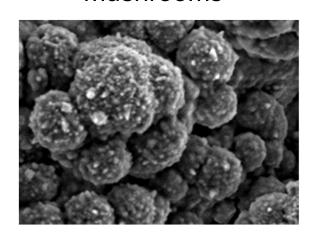
- Elasticity

2D Serpentine pattern

Low Scale
No adhesion
Expensive technology

ogy ++ Very low resistivity

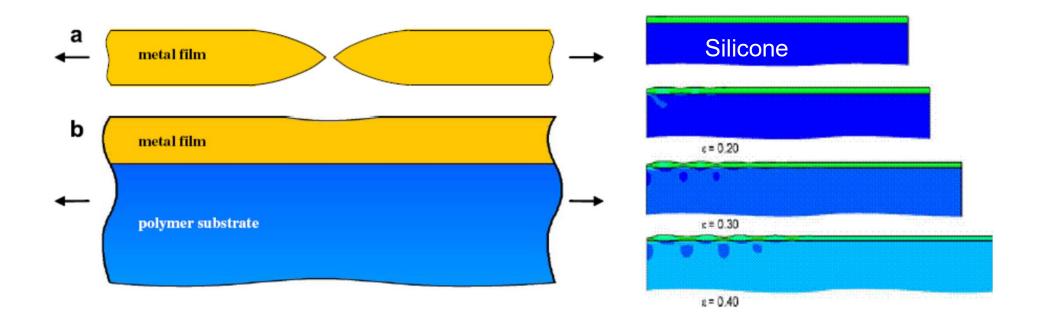
3D structure of mushrooms



Time consuming process



Third ductilization principle: retard or multiply necking

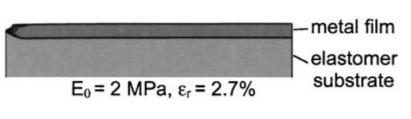


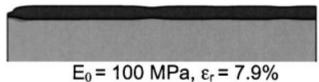
From Suo's group
Li et al., Mech Mater 2005
Li & Suo, IJSS 2006

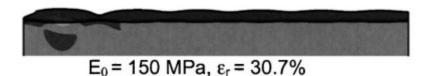
This requires playing with materials characteristics, e.g. strain hardening capacity and rate dependency (see next section of freestanding films)

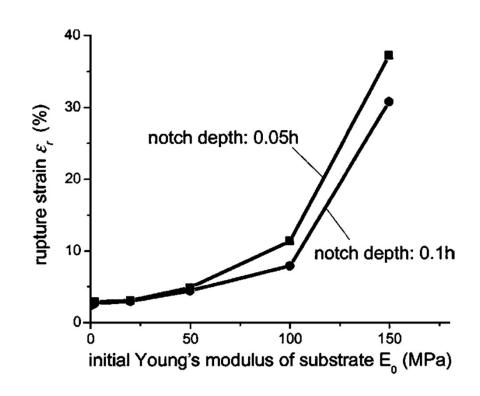


Third ductilization principle: retard or multiply necking









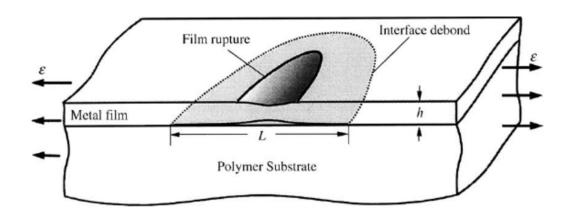
The delocalization process optimisation depends also on stiffness mismatch

Li et al., APL 2004

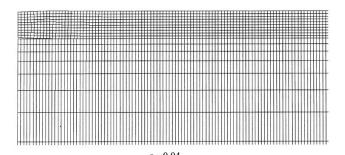
Li & Suo, IJSS 2006

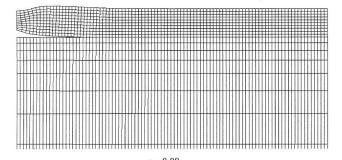


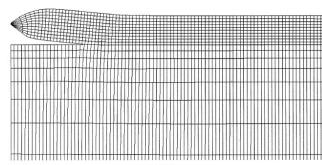
Third ductilization principle: retard or multiply necking



High adhesion needed to avoid freestanding sections of film





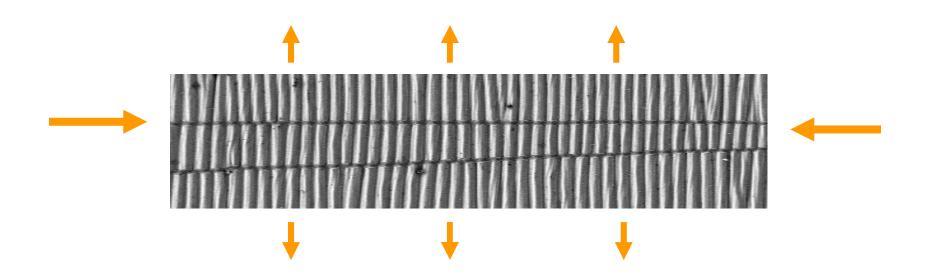




Fourth ductilization principle: favour non percolating crack path

Starting point – why longitudinal cracks?

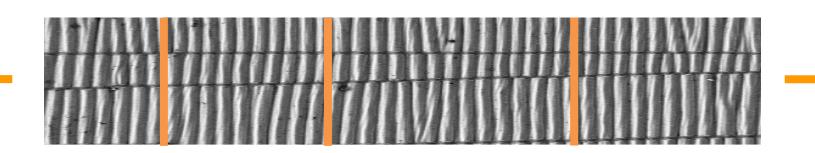
Large tensile stresses build up in the film in the transverse direction due to the transverse extension upon unloading after deposition





Fourth ductilization principle: favour non percolating crack path

If pulling next in longitudinal direction, wrinkles flatten and, then, long transverse cracks develop (depending on film fracture strain and possible – delayed – necking) interrupting electrical conduction





Fourth ductilization principle: favour non percolating crack path

How to avoid long percolating cracks?
One example: tri-branched pre-cracks



Example 1 of combination of strategies : Stretchable helical gold conductor



APPLIED PHYSICS LETTERS 91, 141911 (2007)

Stretchable helical gold conductor on silicone rubber microwire

S. Béfahy, ^{a)} S. Yunus, T. Pardoen, and P. Bertrand *MAPR, Université catholique de Louvain, Croix du Sud 1, 1348 Louvain-la-Neuve, Belgium*

M. Troosters

Neurotech SA, Chemin du Cyclotron 6, 1348 Louvain-la-Neuve, Belgium

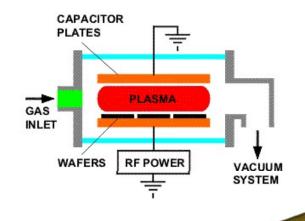


Process

Ph. D. of S. Befahy at UCL, 2006

1. Pre-stretch and pre-twist a silicone wire to favor wrinkles and

2. Oxygen RF cold plasma on prestrained wires



3. Metallization (5nm Ti 80nm Au)

4. Release





Details of Step 2 of process: oxygen RF cold plasma on prestrained wires

to avoid delamination improve adhesion of PDMS

- Challenges
 - Presence of free siloxanes
 - Low surface energy (21-22 mJ/m2)
- Solutions
 - Solvent extraction
 - Surface activation (oxidation)
 - Low pressure plasma
 - UV (atmospheric pressure)
 - Ozone (atmospheric pressure)

Link with lecture 1

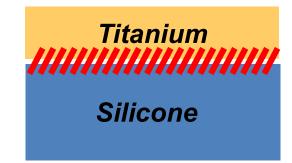




Details of Step 2 of process: oxygen RF cold plasma on prestrained wires

- Challenges
 - Presence of free siloxanes
 - Low surface energy (21-22 mJ/m2)
- Solutions
 - Solvent extraction
 - Surface activation (oxidation)
 - Low pressure plasma
 - UV (atmospheric pressure)
 - Ozone (atmospheric pressure)
 - Titanium or Chromium intermediate thin layer (~5nm)

Link with lecture 1

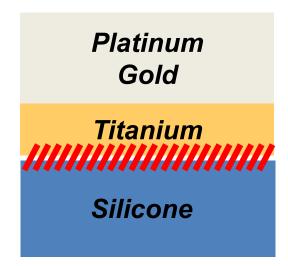




Details of Step 3 of process: deposition

- Metallization by Physical Vapor Deposition
- ~5nm of titanium
- ~100nm of platinum or gold

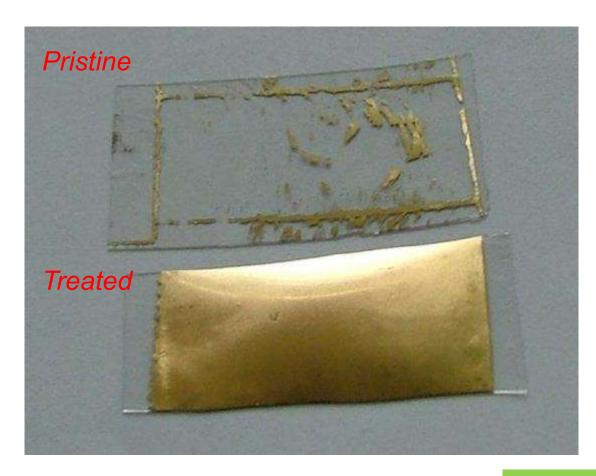






Good adhesion!

Peel Scotch test

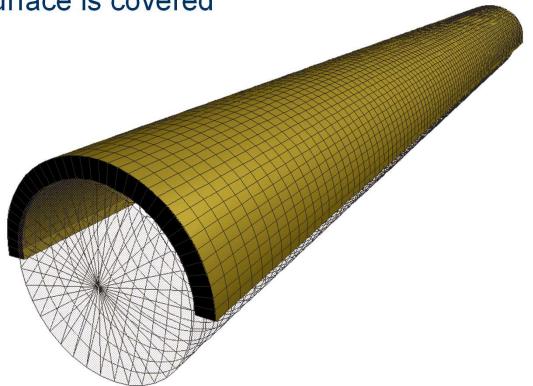




Details of Step 3 of process: deposition

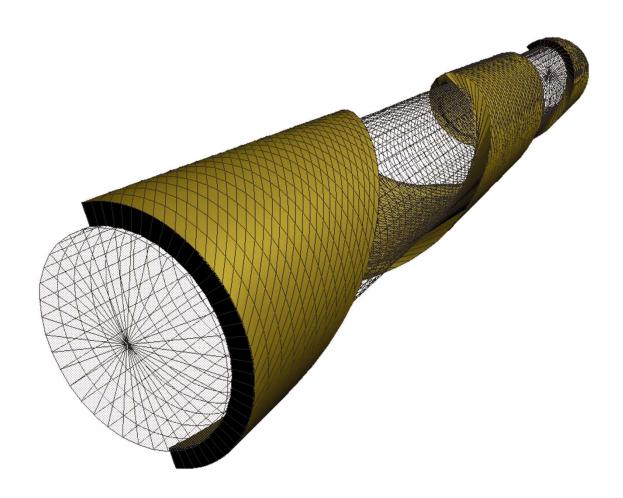
• 5nm Ti and 80nm Au

· Half the surface is covered



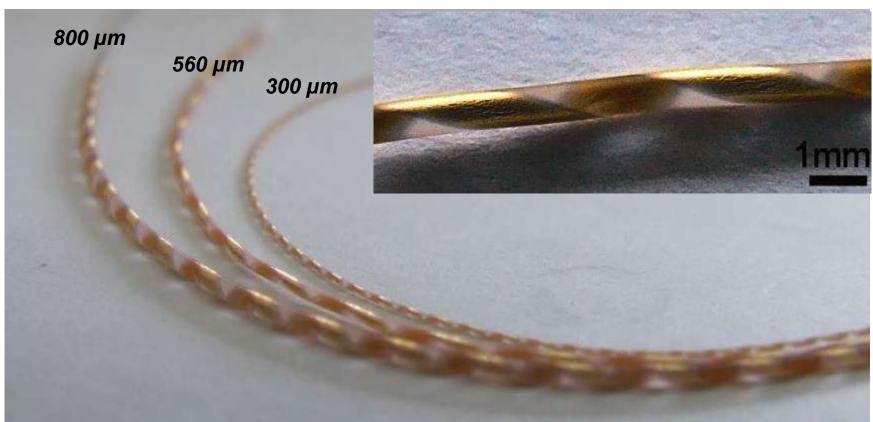


Details of Step 4 of process : release





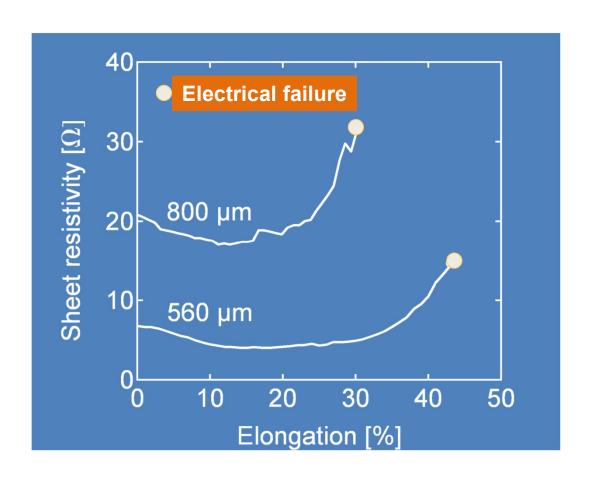
In real



Patent PCT/EP2007/053159



Performances of the wires



9mm long 20 full rotations 25% of stretch Two different diameters

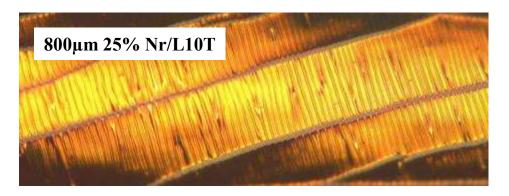
- 800µm diameter more stretchable
- at least 30% stretchability
- a minimum in the evolution of the resistance
- No sharp increase in resistance

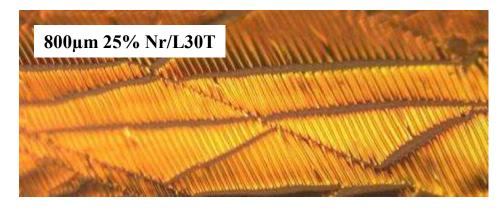
Befahy et al., APL 2007

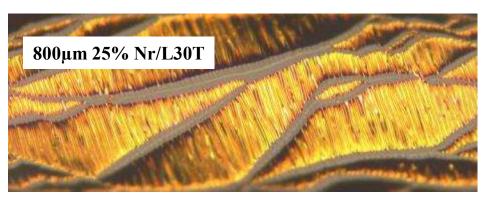
Ph. D. of S. Befahy at UCL, 2006



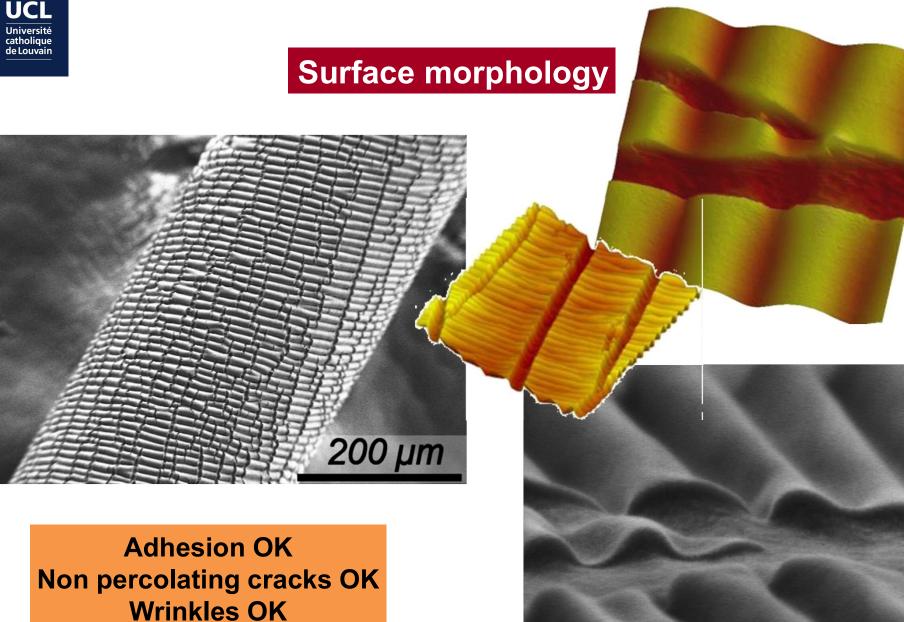
Quantitative characterization of cracking pattern









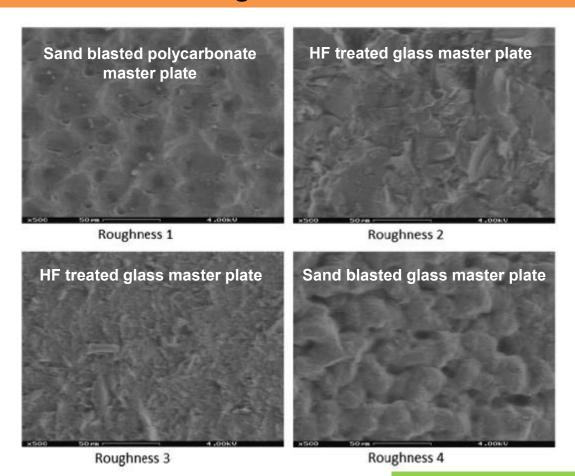


Befahy et al., APL 2007



Example 2 of combination of strategies

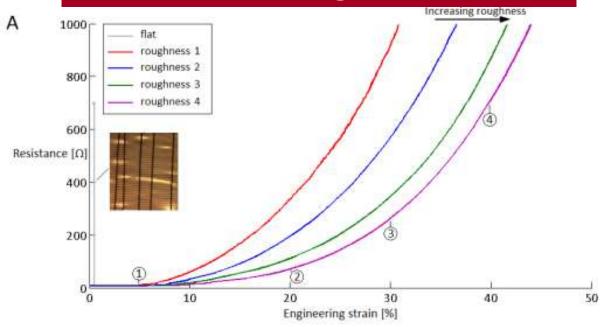
Idea: play with substrate roughness to randomize crack pattern

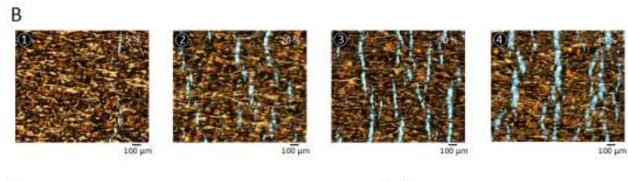


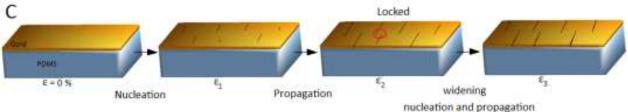
Lambricht, Pardoen, Yunus, Acta Mater 2013



Example 2 of combination of strategies



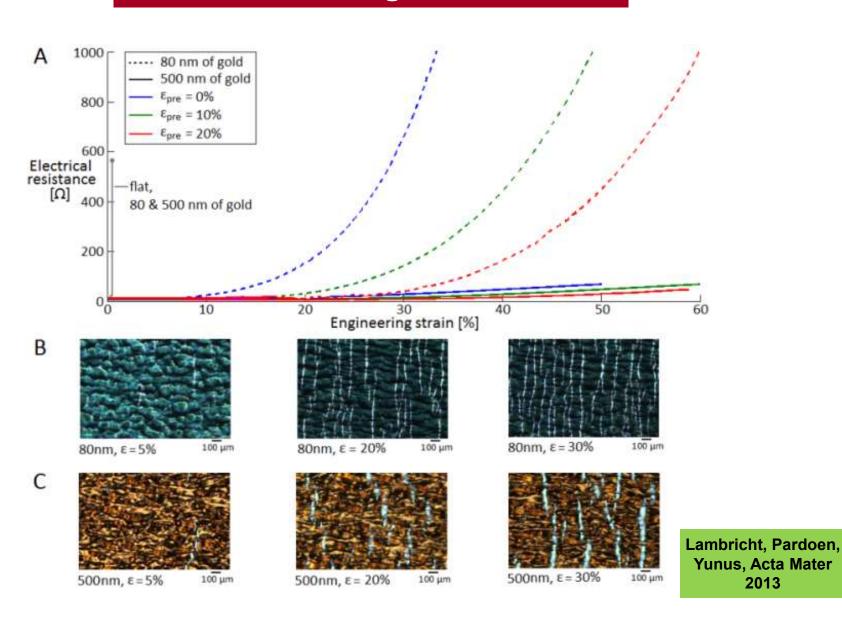




Lambricht, Pardoen, Yunus, Acta Mater 2013



Example 2 of combination of strategies





Approach 1 : Thin films on substrate Conclusion

Pro and cons

Easy to manipulate at macro level

Adapted to macro testing devices

Closer to a system property – to explore extrinsic effects

Difficulties to deconvolute substrate effects to estimate e.g. hardness or fracture toughness

Difficult to extract stress level

Careful with internal stress



Outline

1. Introduction

2. Fracture of films on substrates

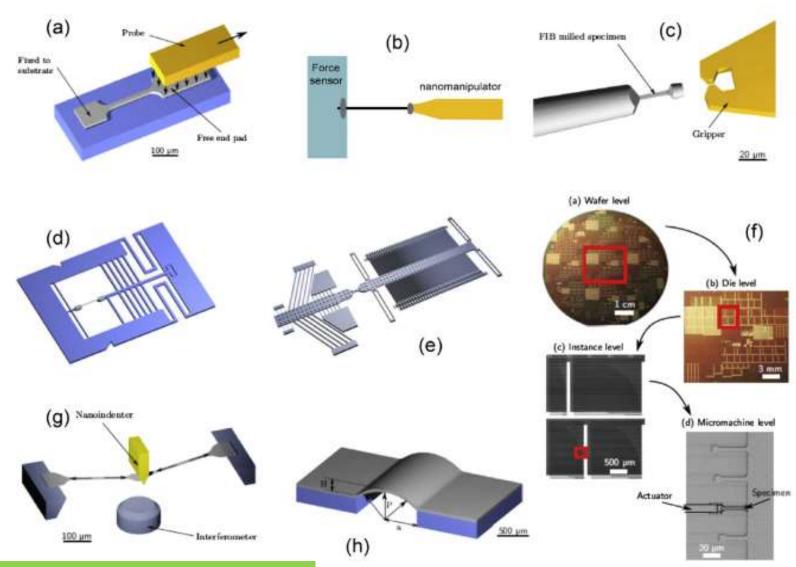
- test methods and extraction of G
- example 1 : CrN on polymer (indentation)
- example 2 : SiN on polymer (subcritical crack growth)
- example 3 : Au on polymer (for flexible electronics)

3. Fracture of freestanding films

- Test methods for measuring the fracture strength strain
- fracture strength of brittle films
- fracture strain of ductile films
- fracture toughness



Approach 2 : Mechanical testing of freestanding small scale objects



See ref in Pineau, Benzerga, Pardoen, Acta Mater 2016



UCLouvain method: Fabrication of an elementary on chip micro- or nano- test structure

Start with Si wafer



Top view





Deposition of sacrificial layer (e.g. SiO₂)



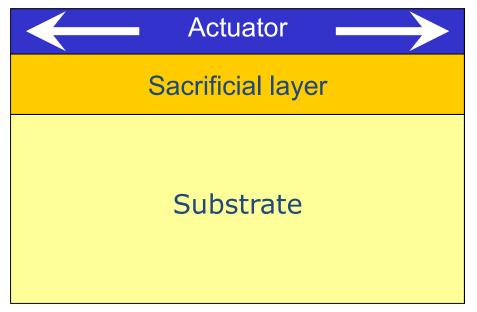
Top view

Sacrificial layer

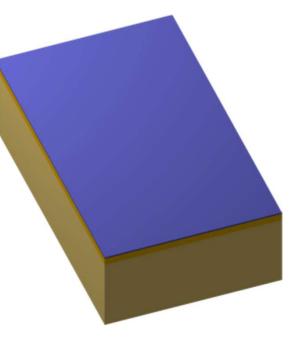
Substrate



Deposition of the actuator layer involving large internal tensile stress (e.g. Si_3N_4)



Cross section view



Top view

Stoney method to measure $\sigma^{internal}$



First photolithography



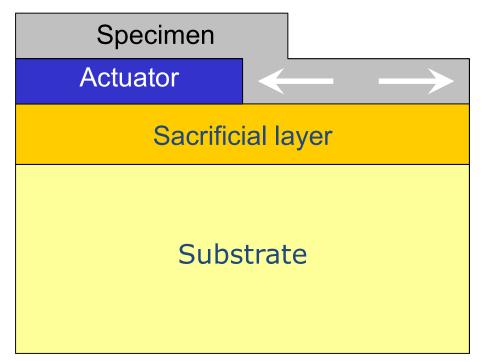
Sacrificial layer

Substrate

Top view



Deposition of test material



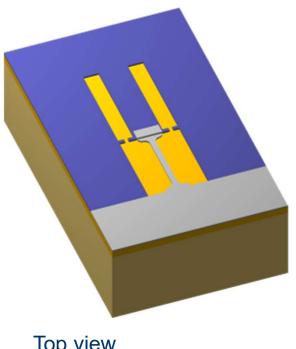
Top view

Stoney method to measure $\sigma^{internal}$



Second photolithography

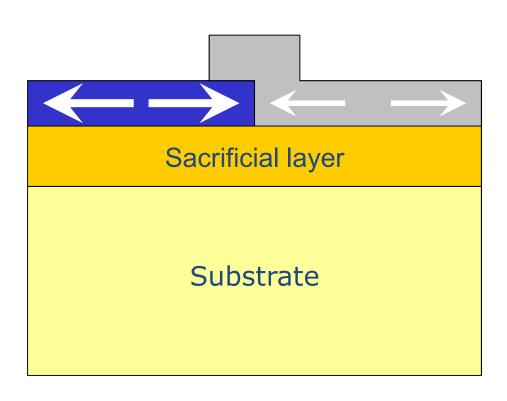
Actuator Sample Sacrificial layer Substrate

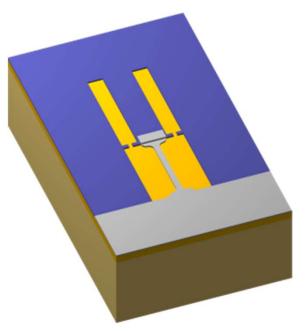


Top view



Starting point of the tensile test

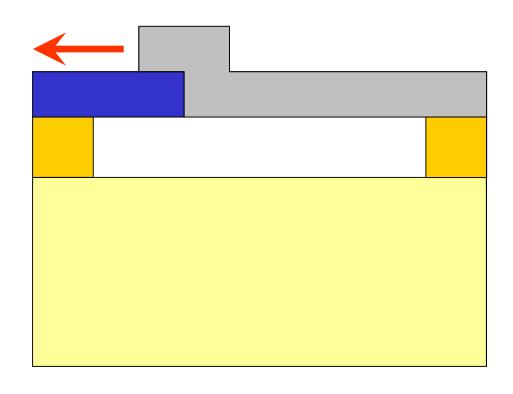


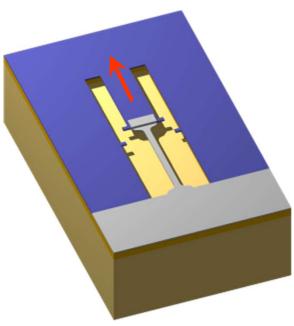




Release of the structures

(e.g. HF wet etching)

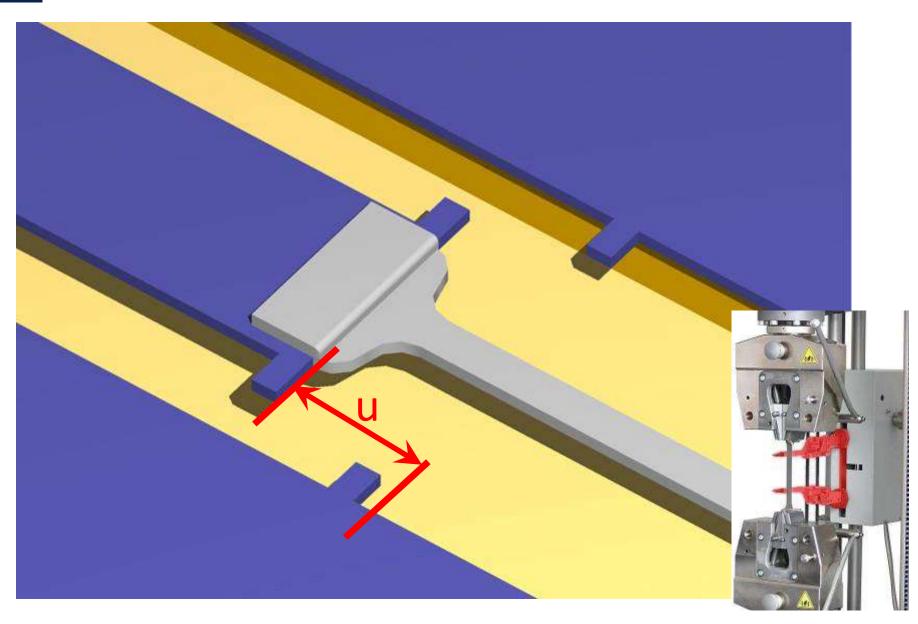




- Critical: etching selectivity
- Actuator is wider and specimen is thus released first
- Strain rate is not controlled

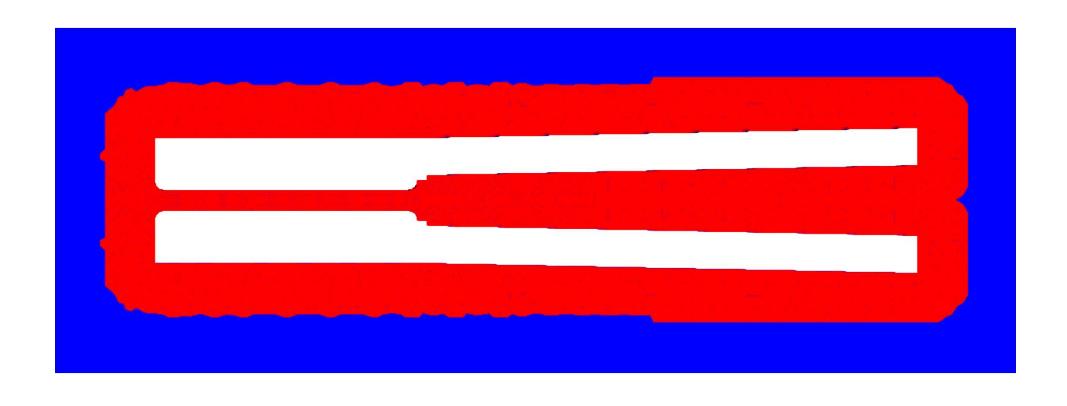


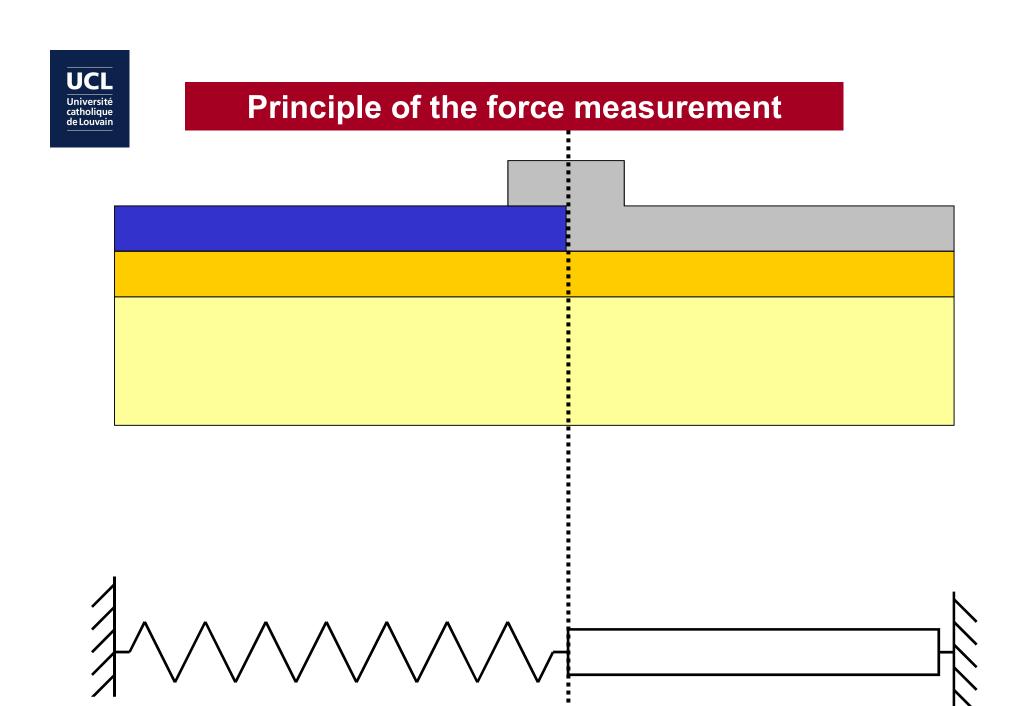
Measurement of displacement





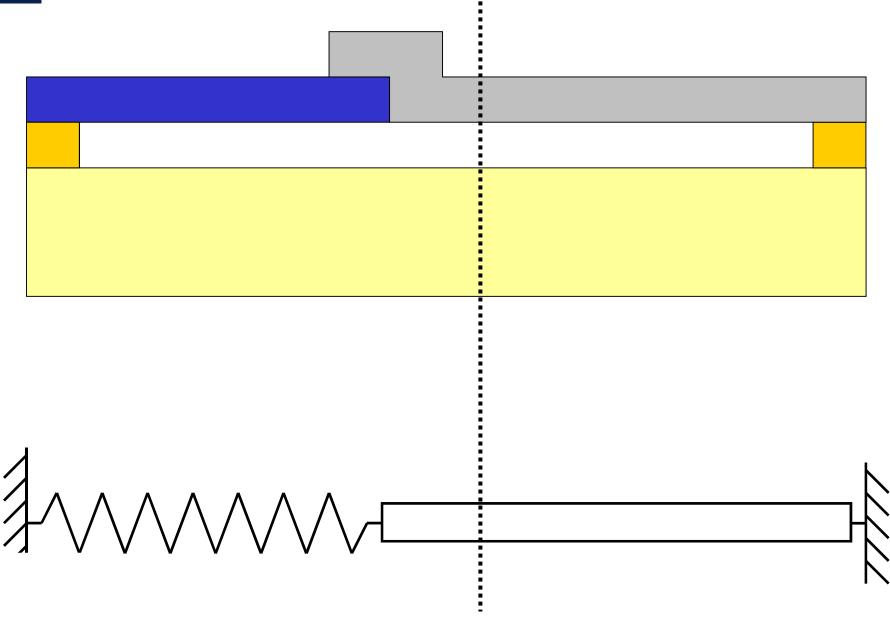
Simulations of the release process



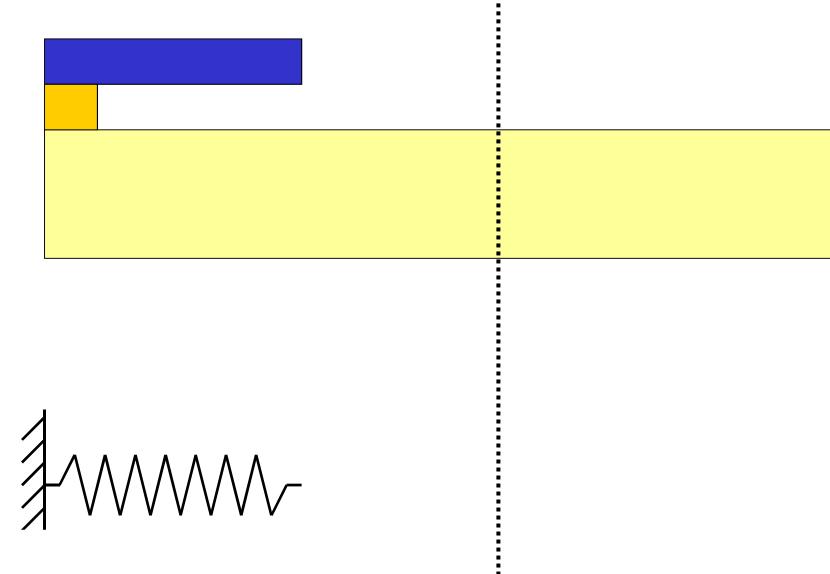


S. Gravier et al., JMEMS, vol. 18 (2009) 555

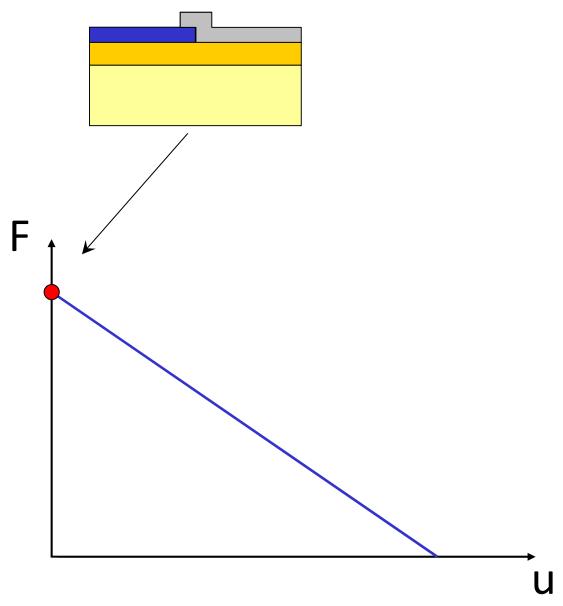




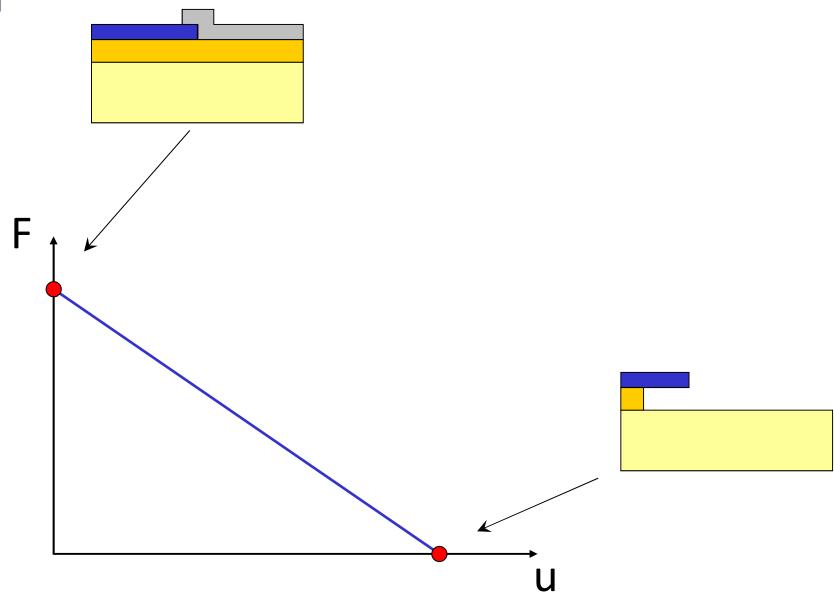




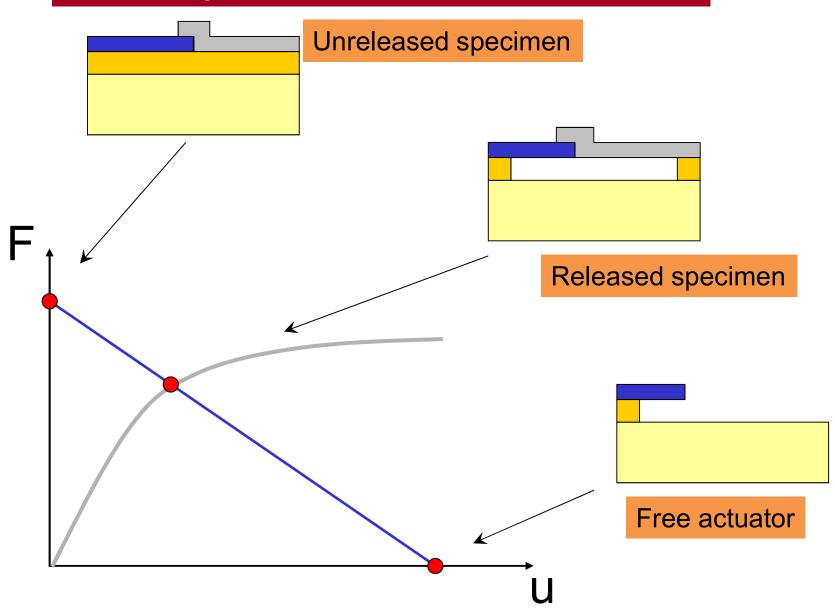




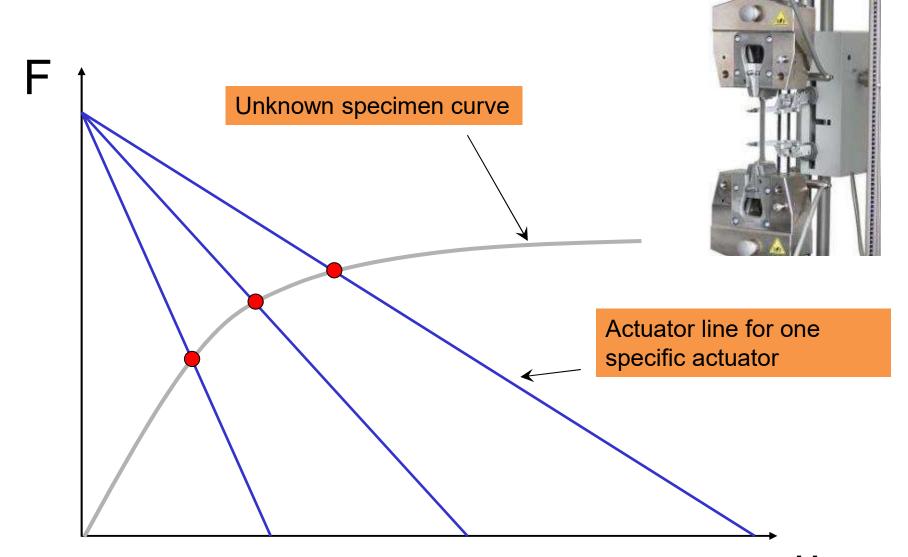




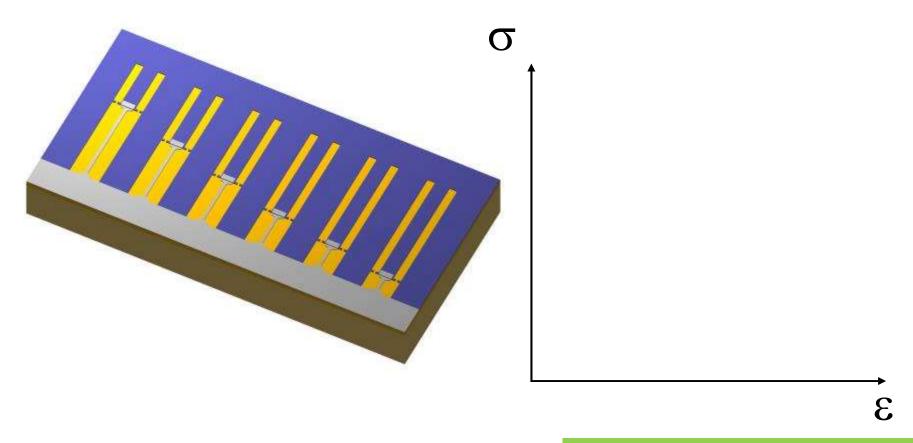




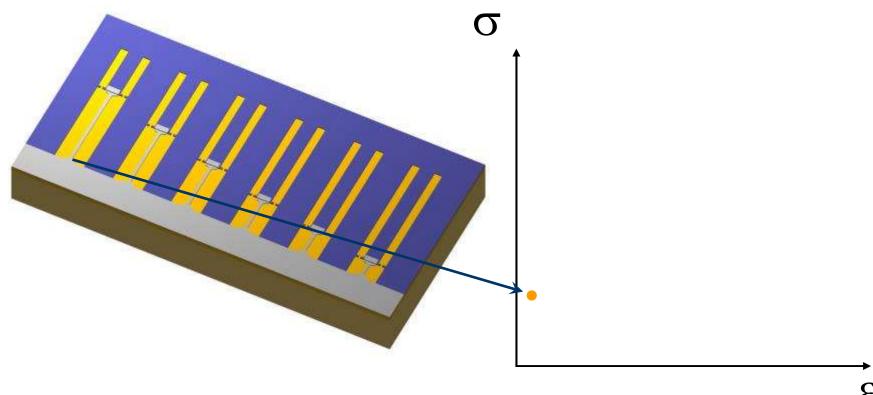




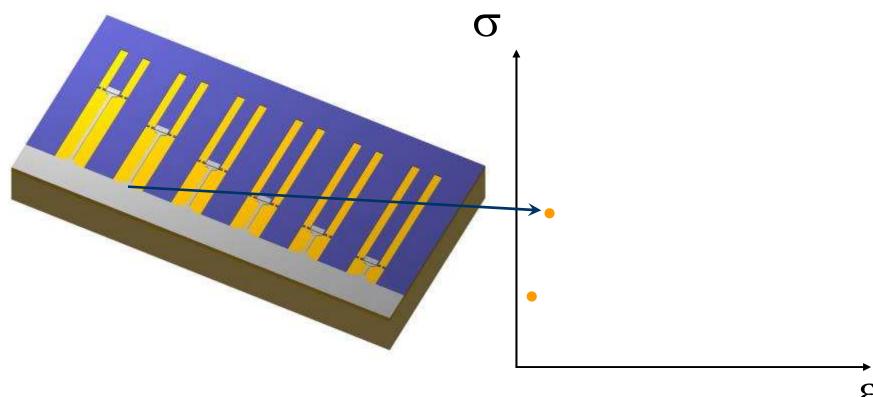




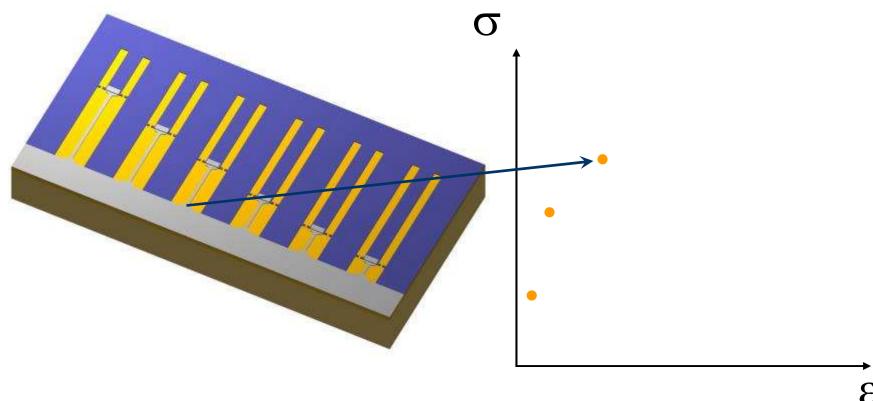




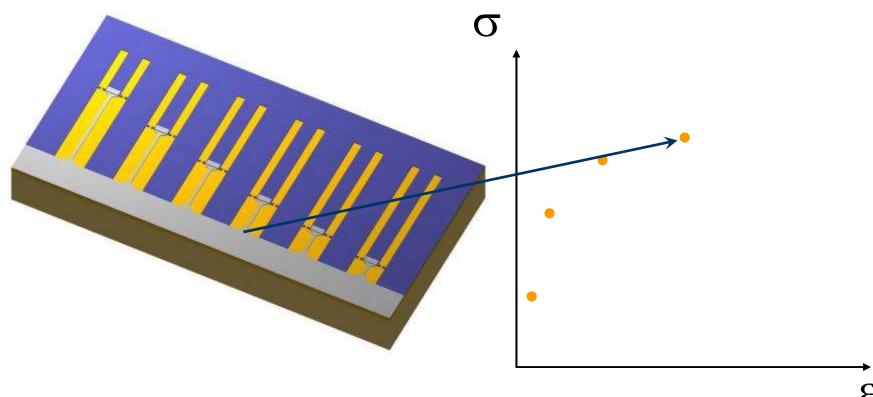




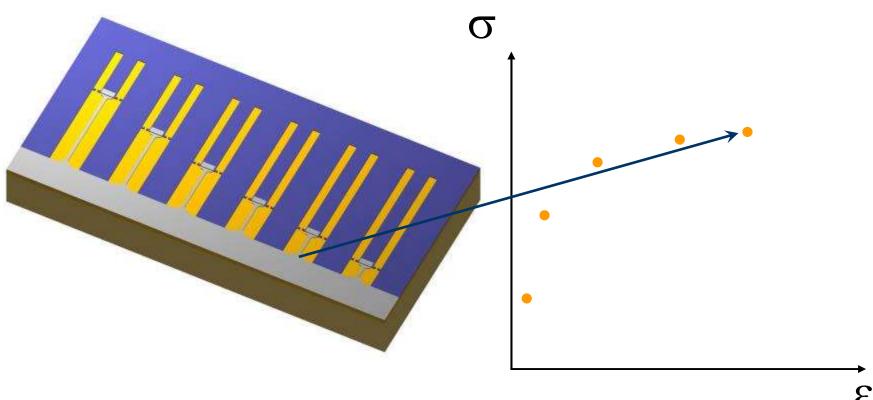








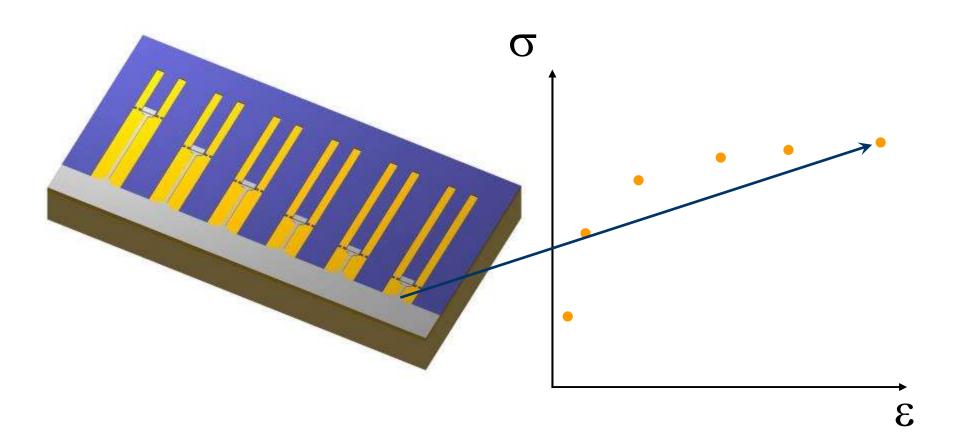






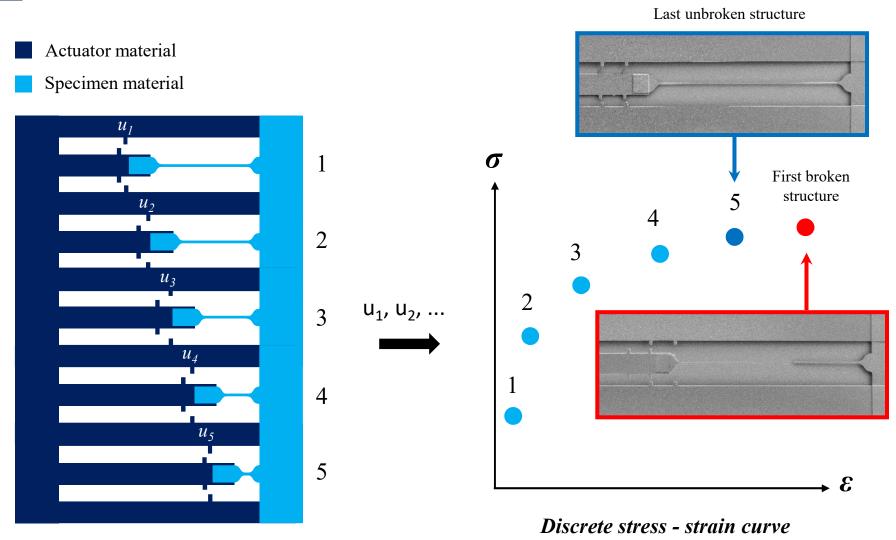
From single tensile stage to full stress strain curve determination

Both actuator and sample length can be varied.



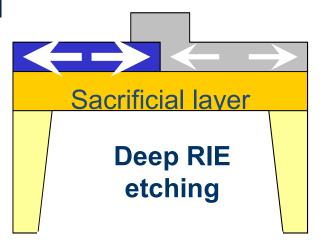


Determination of fracture strain

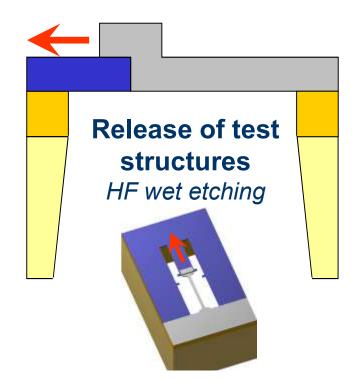


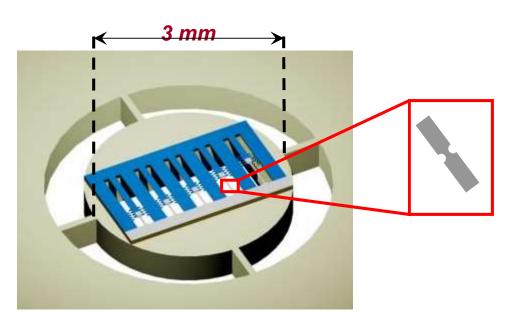


Extension to in- or ex- situ TEM analysis

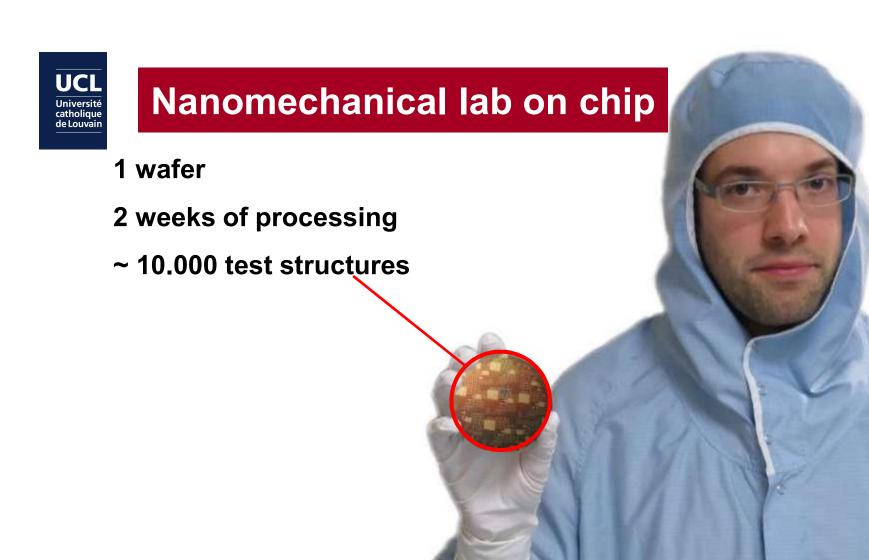








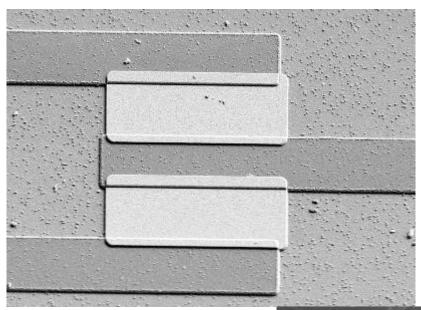
Colla et al., Nature Comm 2015

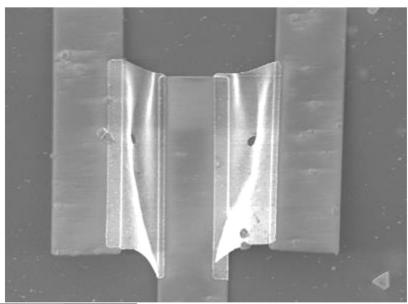


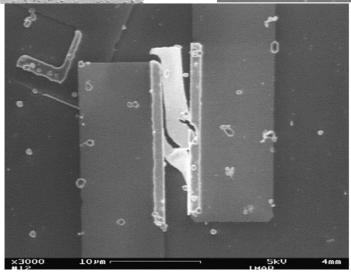




Shear tests

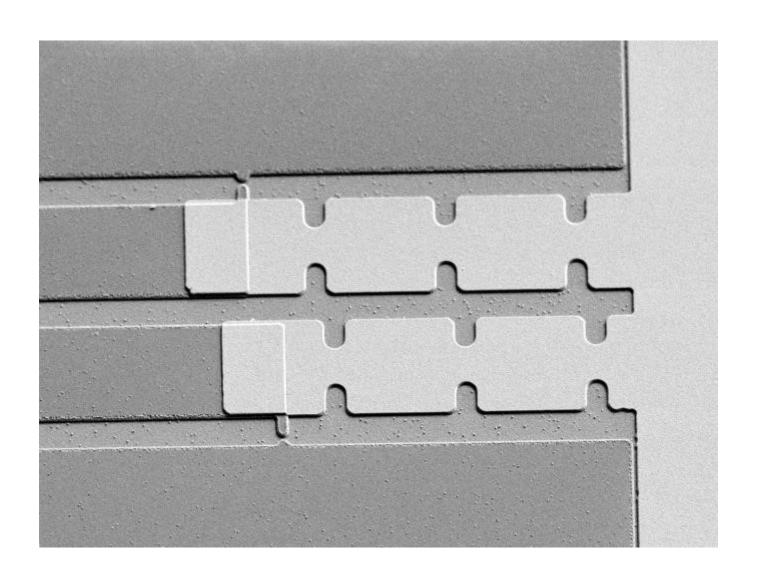






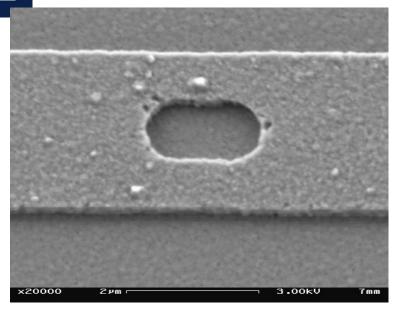


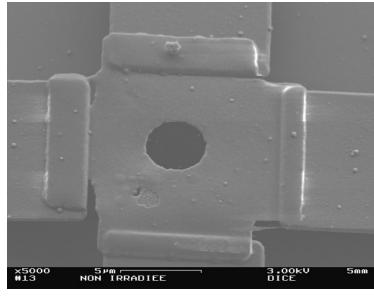
Notched specimens

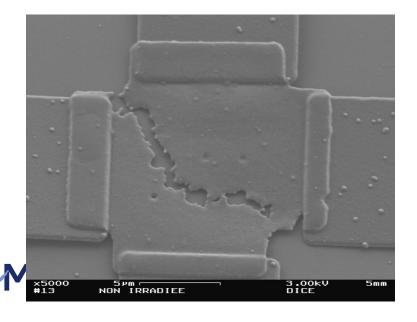


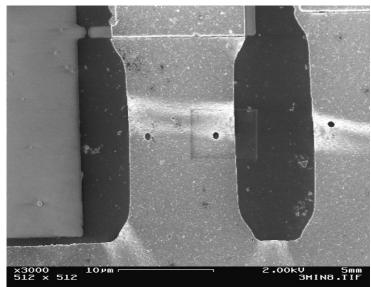
UCL Université catholique de Louvain

- and many others ... -



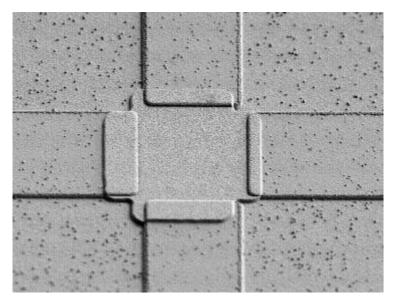


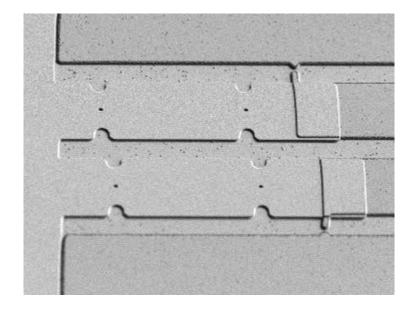


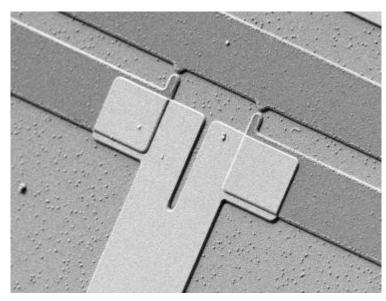


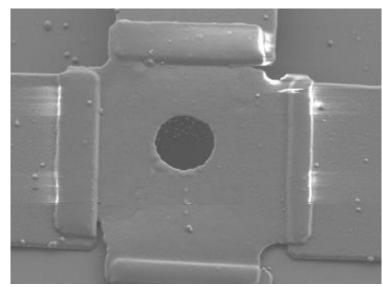


and many others...





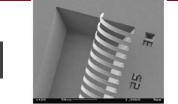






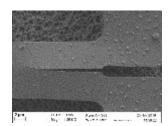
UCL On chip nanomechanical testing platform

Internal stress

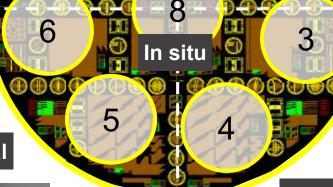


Electromechanical couplings

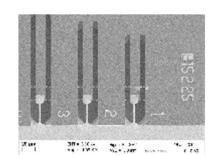




Fracture mechanics

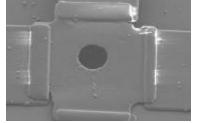


Uniaxial tension

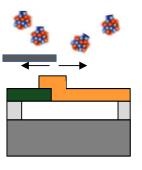


Creep

Multiaxial



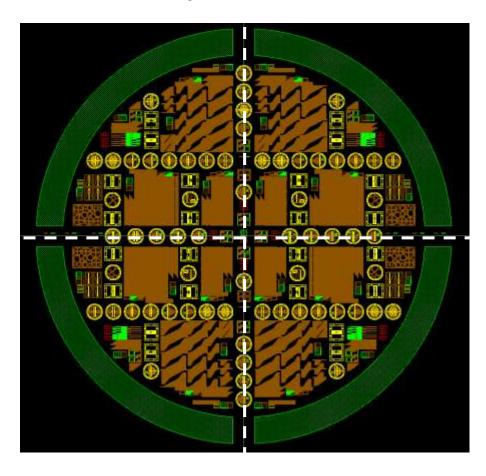
Irradiation creep





Lab-on-chip platform – Last generation (#8)

Global top view of the last generation masks 3 inches wafer



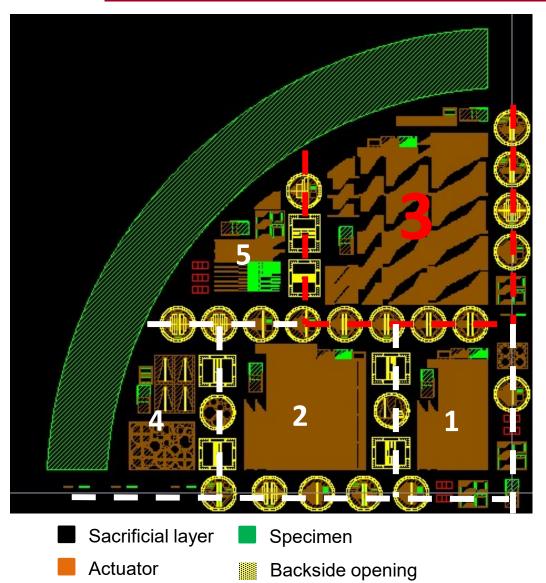
4 equivalent areas

All the structures are repeated 4 times

4*22 TEM compatible sets on 1 wafer



Lab-on-chip platform – Last generation (#8)



window

Platform 1, 2 and 3: uniaxial tensile testing for brittle and ductile materials oLarge PAD dedicated to measure the thickness

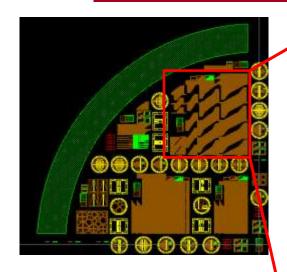
oStructures to extract the mismatch strain and the Young's modulus

Platform 4: Shear and biaxial tensile testings

Platform 5: Structures to extract the mismatch strain, pillars, single and double clamped beams



Lab-on-chip platform – Last generation (#8)



- Sacrificial layer
- Actuator
- Specimen
- Backside opening window

Structures of interest

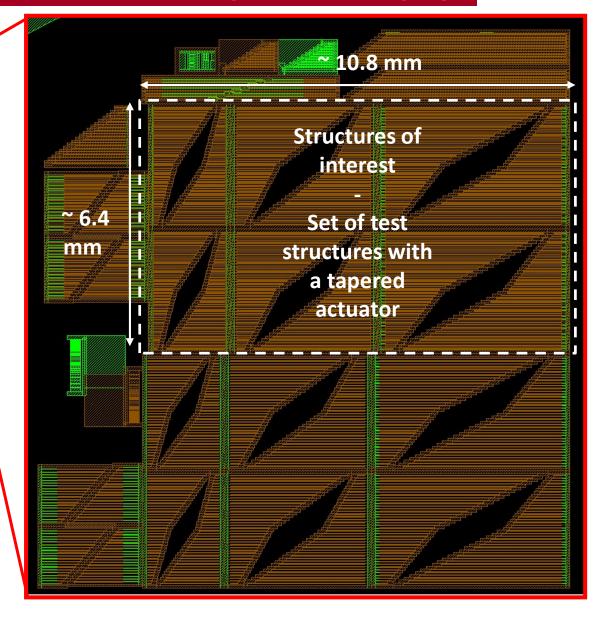
12 sets of 40 micromachines

→ 3 specimen lengths : 25,

50 and 100 μm

 \rightarrow 4 specimen widths : 1, 2,

4. 6 um





Outline

1. Introduction

2. Fracture of films on substrates

- test methods and extraction of G
- example 1 : CrN on polymer (indentation)
- example 2 : SiN on polymer (subcritical crack growth)
- example 3 : Au on polymer (for flexible electronics)

3. Fracture of freestanding films

- Test methods for measuring the fracture strength strain
- fracture strength of brittle films
- fracture strain of ductile films
- fracture toughness



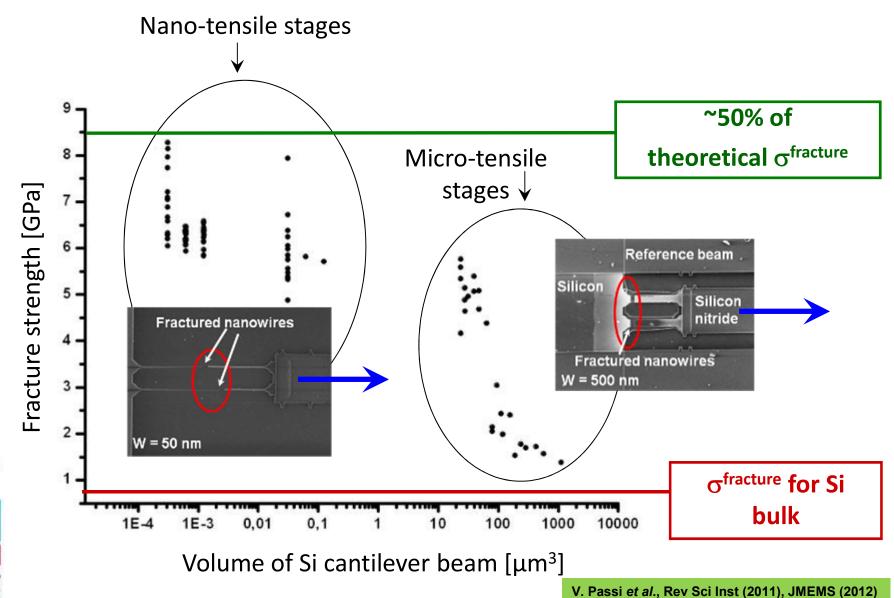
Example 1 : Fracture strength of PolySi

(PolySi is THE enabling structural material for MEMS devices)



winfab

Start with single crystal Si micro and nanowires

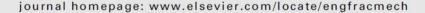


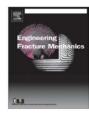




Contents lists available at ScienceDirect

Engineering Fracture Mechanics

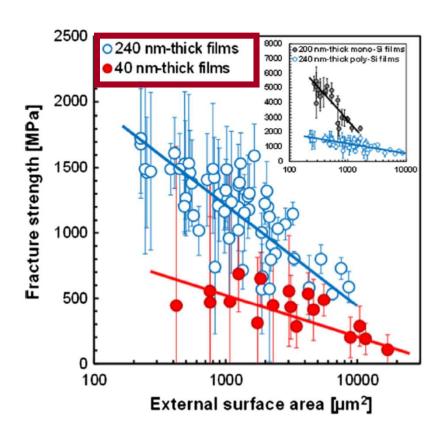


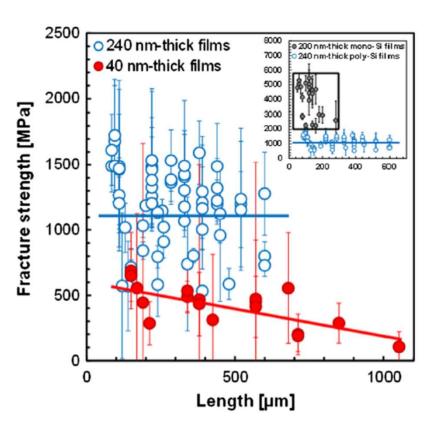


Size dependent fracture strength and cracking mechanisms in freestanding polycrystalline silicon films with nanoscale thickness



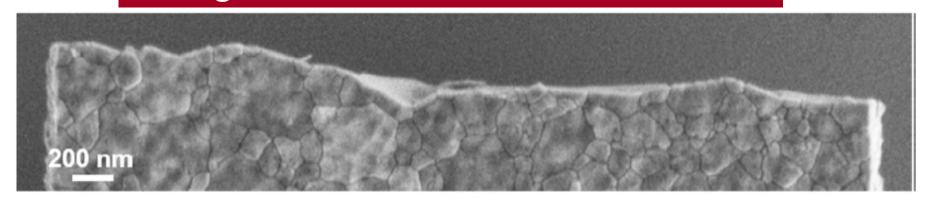
R. Vayrette a,b,*, M. Galceran c,d, M. Coulombier a, S. Godet d, J.-P. Raskin b,e, T. Pardoen a,e



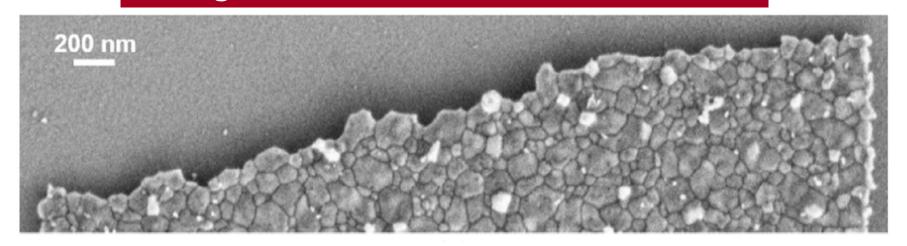




transgranular fracture in 240nm thick film



intergranular fracture in 40nm thick film

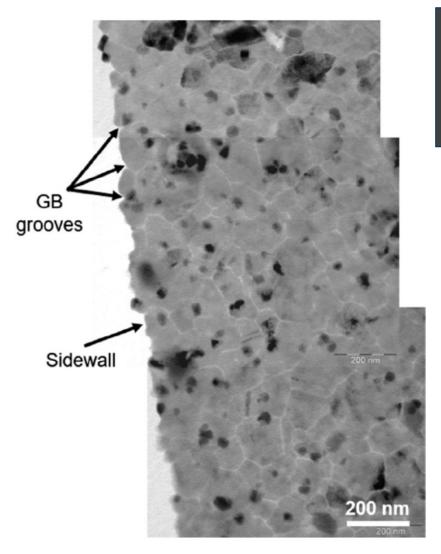




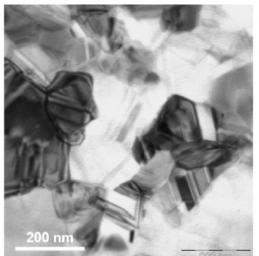
Why trans- versus inter-?

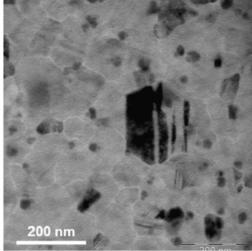
by ACOM-TEM

Thickness (nm)	HAGB (%)	CSLB (%)	Σ3 (%)	LAGB (%)
240 40	64.2	30.2	14.5	5.6
40	70.4	23.7	9.8	5.9



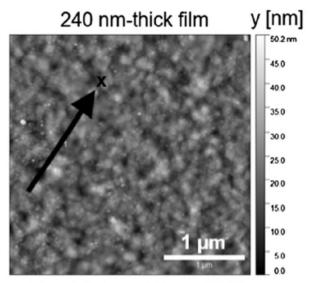
- Same distribution of GB character
- Similar crystallite size
- More twin lamellae in 240 nm thick
- GB grooves on both types of films



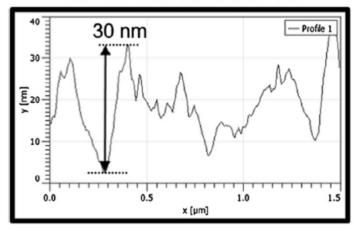


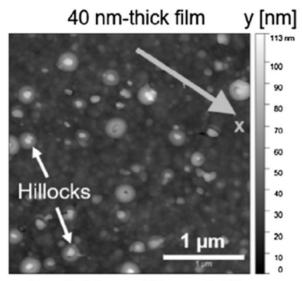


Why trans- versus inter-?

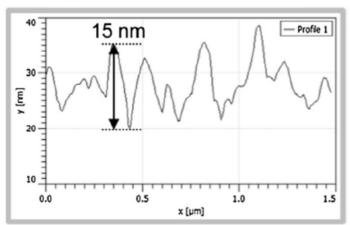


Ra: 4.39 nm / Rms: 5.57 nm





Ra: 3.34 nm / Rms: 4.33 nm



We believe (!) that the larger relative amplitude of GB grooving in the 40nm thick film is the reason for the transition to intergranular fracture



To go deeper on PolySi fracture, the advise is to consult the excellent studies performed at Sandia Laboratory

APPLIED PHYSICS REVIEWS 2, 021303 (2015)

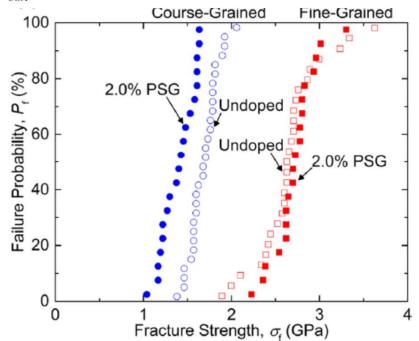
APPLIED PHYSICS REVIEWS

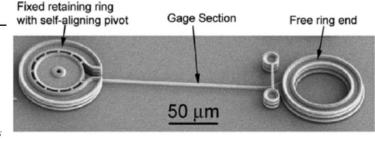
Fracture strength of micro- and nano-scale silicon components

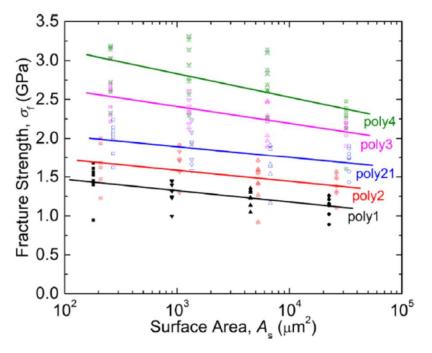
Frank W. DelRio, 1,a) Robert F. Cook, 2,b) and Brad L. Boyce 3,c)

¹Applied Chemicals and Materials Division, Material Measurement Laboratory, National Institute of Standards and Technology, Boulder, Colorado 80305, USA

³Materials Science and Engineering Center, Sandia National Laboratories, Albuquerque, New Mexico 87185, USA







²Materials Measurement Science Division, Material Measurement Laboratory, National Institute of Standards and Technology, Gaithersburg, Maryland 20899, USA



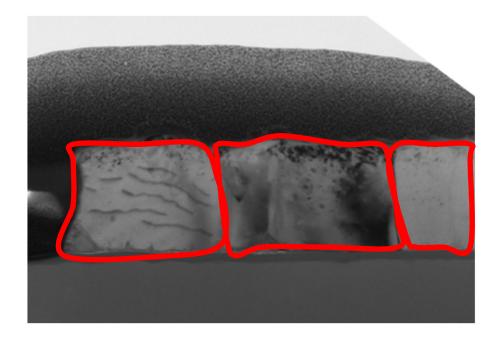
Example 2 : fracture strain of Al thin films



Example of Al films

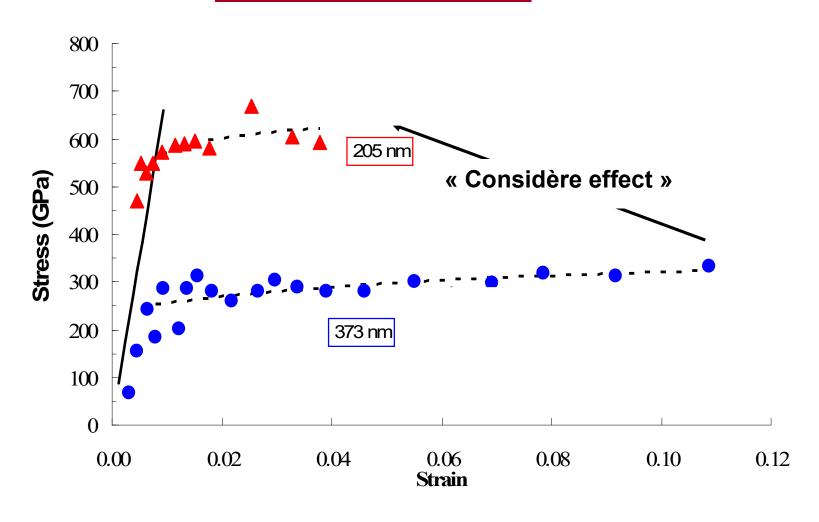
Pure AI evaporated films
2 thicknesses = 205 and 373 nm, grain size ≈ 180 and 230 nm

AlSi1% evaporated films thickness = 200 nm, grain size ≈ 200 nm





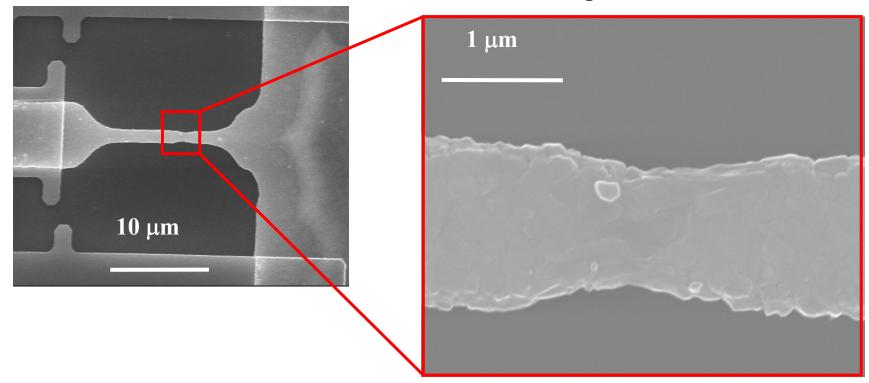
Example of AI films





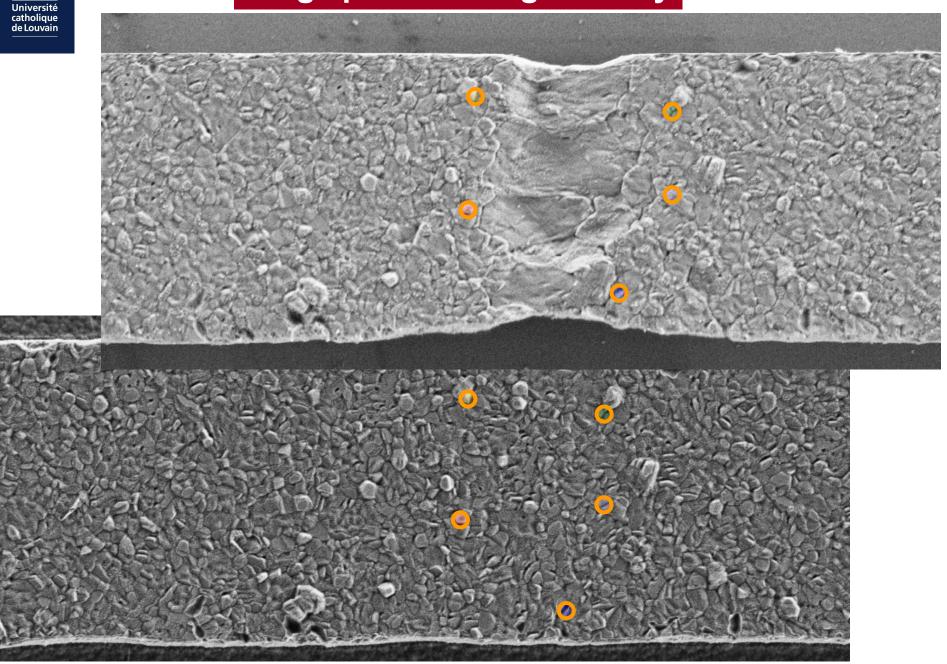
Clear evidences of stable necking

elongated neck!

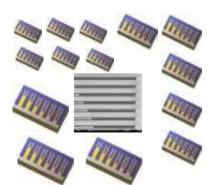




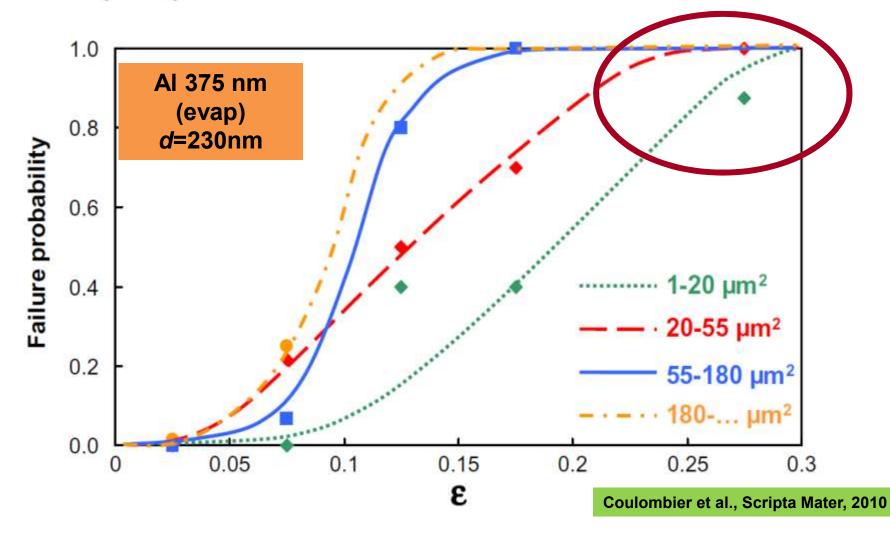
Large post necking ductility





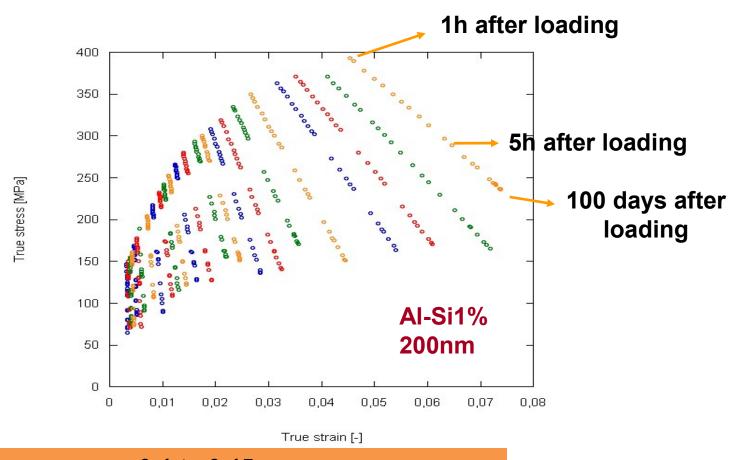


In some specimens, fracture strain near 30%





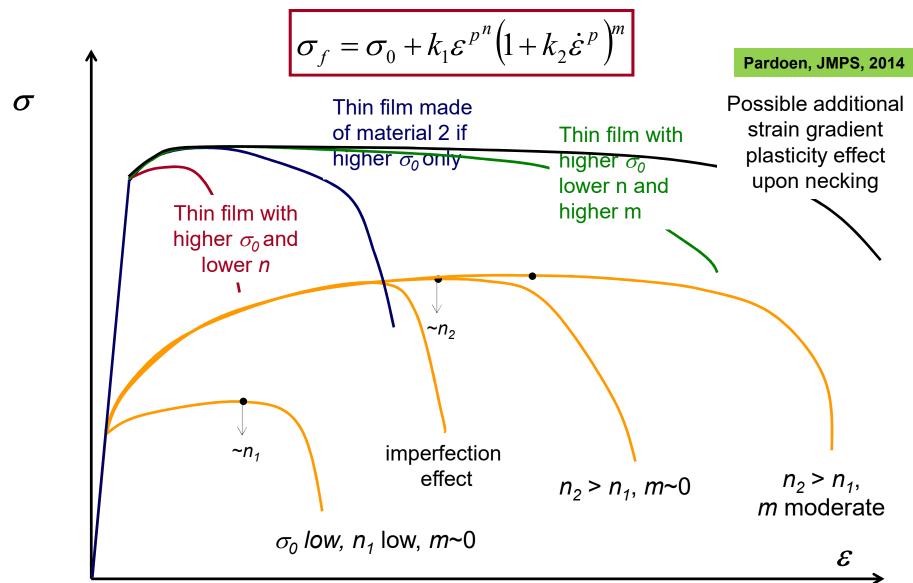
Relaxation tests on AISi 1%



m ≈ 0.1 to 0.15
Even larger in pure Al (too fast to be measured)
(as explained by thermally activated deformation mechanisms, involving grain growth)

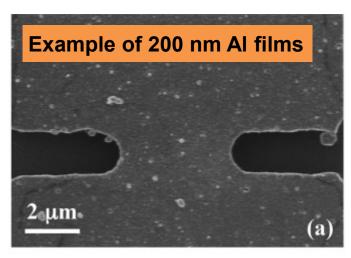


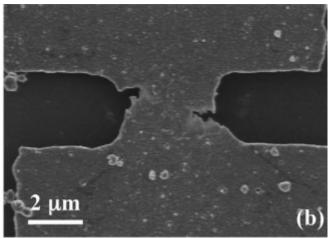
The big picture on necking

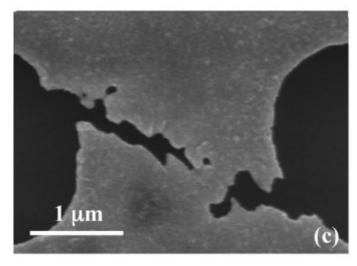


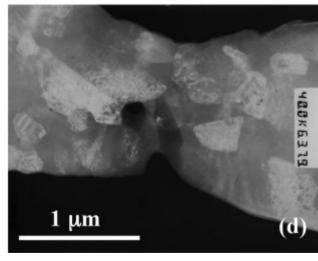


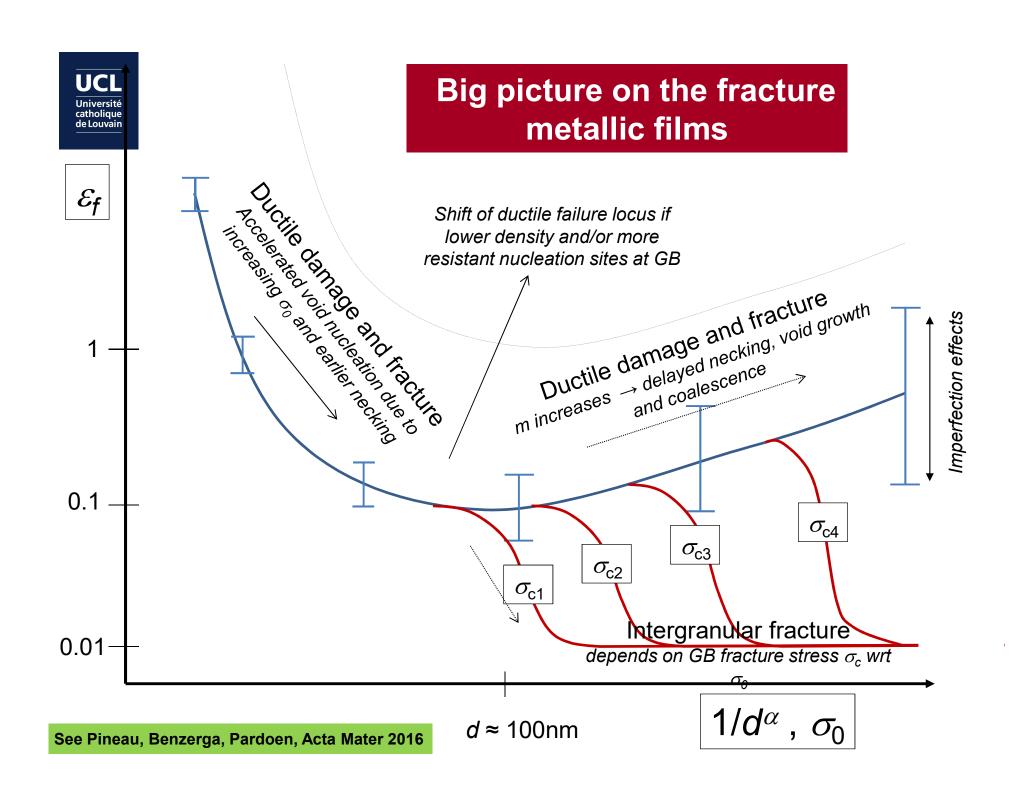
Metallic films fracture and nanowires by damage at GB













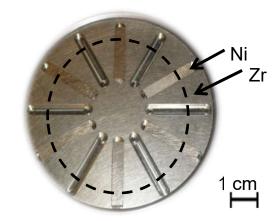
Example 3 : fracture of ZrNi metallic glass films



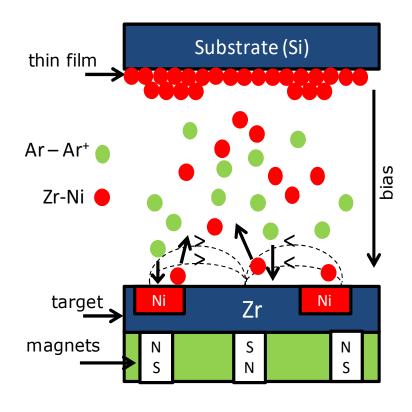
Zr₆₅Ni₃₅ films

DC-magnetron sputtering

at Plateforme Technologique Amont (PTA), Grenoble







Composition control

(Electron Problem Micro Analysis, EPMA)

- No impurities
- Uniform composition along the substrate

Zr₆₅Ni₃₅ (%at.) composition

Thickness control

(cross-section SEM + mechanical profilometer)

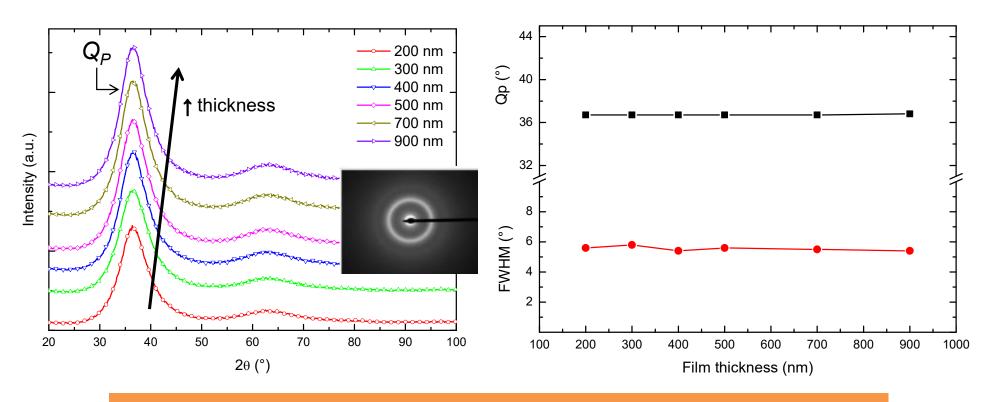
Linear growth rate ~ 1 nm/s

Thickness ranges from 200 to 900 nm



Zr₆₅Ni₃₅ films

DC-magnetron sputtered with thickness between 200 and 900 nm



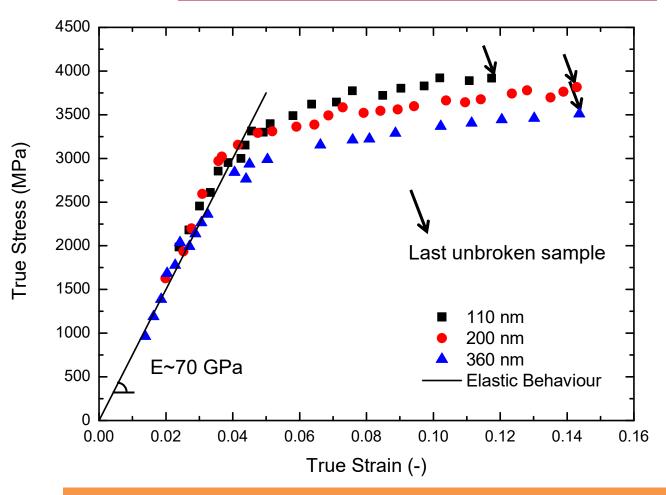
Amorphous structure (presence of diffuse halos)

No peak shift (Q_P) and same FWHM for different thicknesses

→ atomic structure independent of thickness



Uniaxial tension response of 360 nm-thick Zr₆₅Ni₃₅ film



Actuator thickness 160 nm

Actuator length variable

Actuator width 15 μm

Specimen width 1 or 2 µm

Specimen length 25 µm

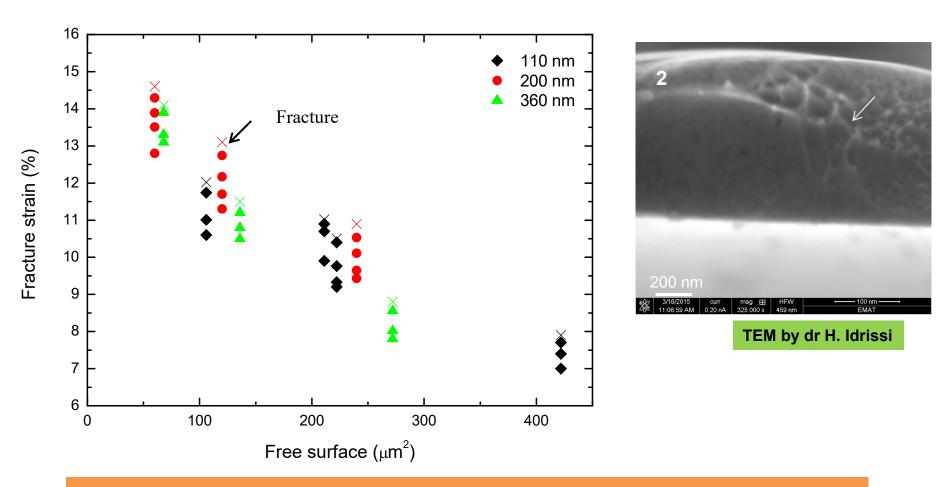
Elastic behavior up to 4% with E ~ 70 GPa (OK Brillouin spectro)

Large fracture strain up to 15% (decreasing with increasing length)

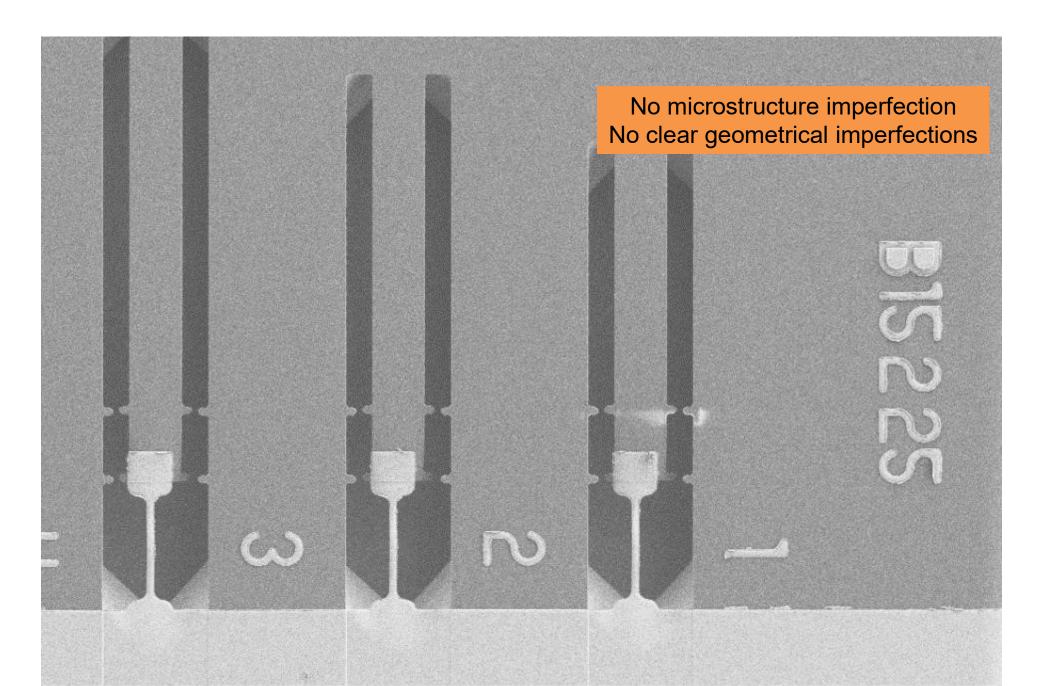
Yield stress around 2900 MPa



Fracture strain decreases with increasing specimen free surface



TEM shows no evidence of shear bands
Fracture surface involve flat regions and corrugations (dimples)



20 μm

EHT = $3.00 \, \text{kV}$

Mag = 1.08 K X

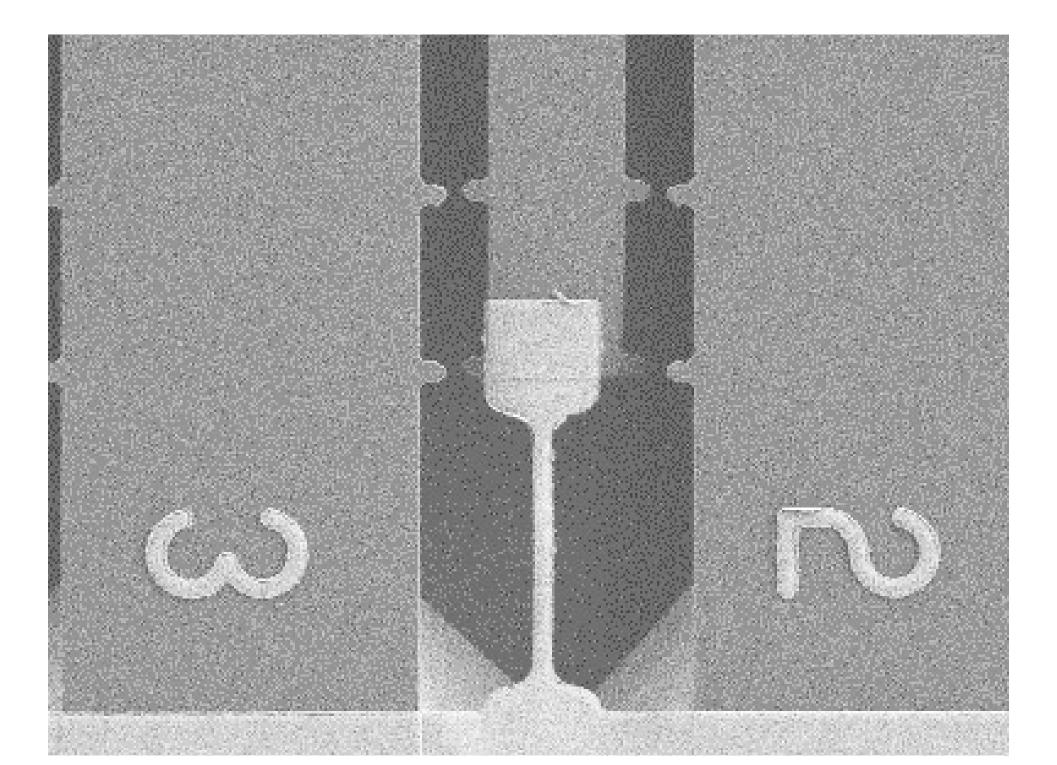
Signal A = SE2

 $WD = 3.0 \, mm$

18 Jul 2014

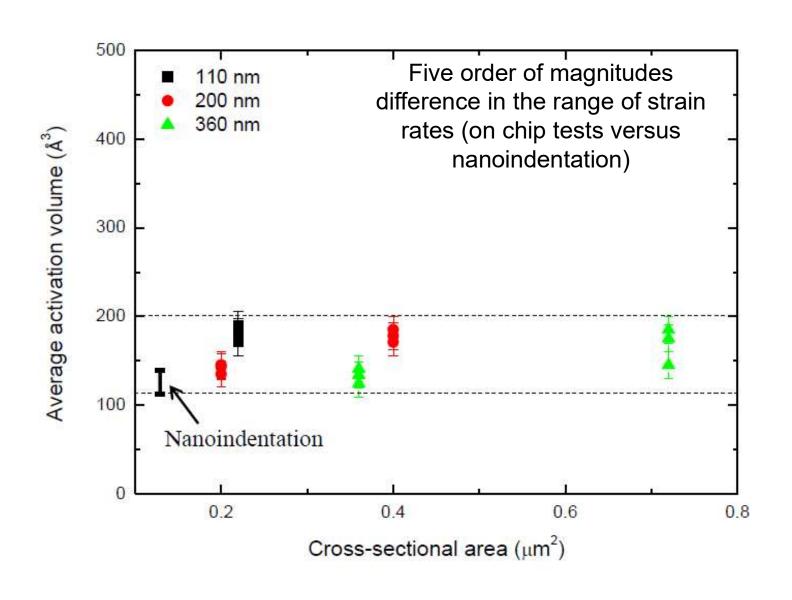
Aperture Size = 30.00 µm

10:10:30



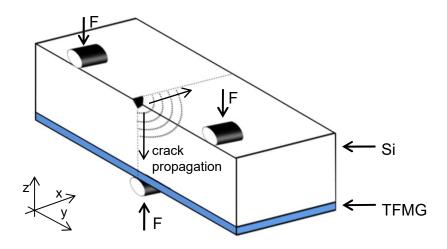


Confirmation of the high rate sensitivity measured by nanoindentation





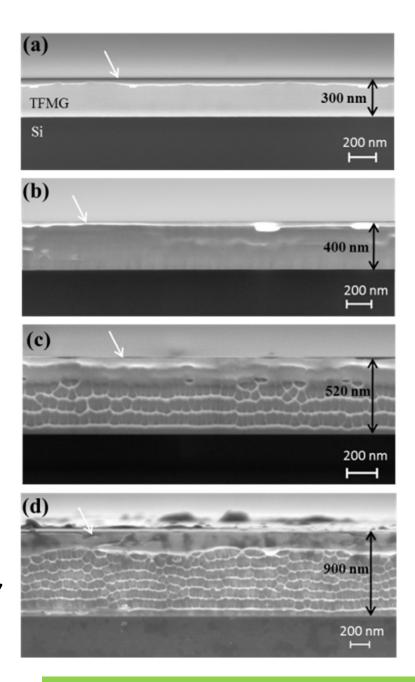
Method: crack propagation from substrate + SEM observation



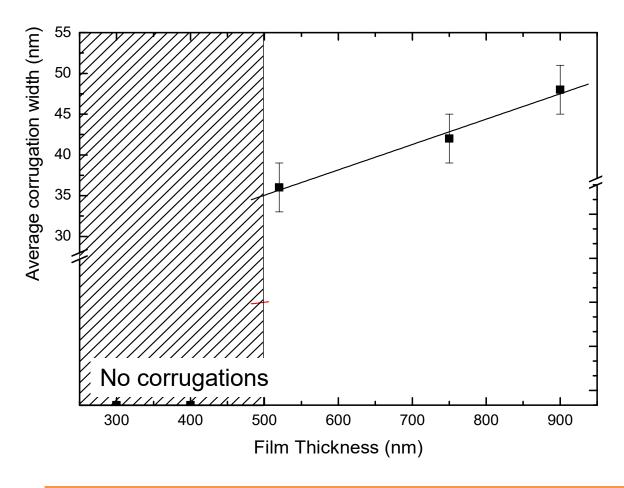
Film thickness †

Corrugation pattern formation for thickness ≥ 500 nm

Presence of a folded layer for all thicknesses







Fracture toughness estimated by

$$K_c = \sigma_v \sqrt{40w}$$

*K*_c → Fracture toughness

 $\sigma_{V} \rightarrow \text{Yield strength}$

 $w \rightarrow$ corrugation width

Xi et al., Phys. Rev. Lett. 94, 125510 (2005)

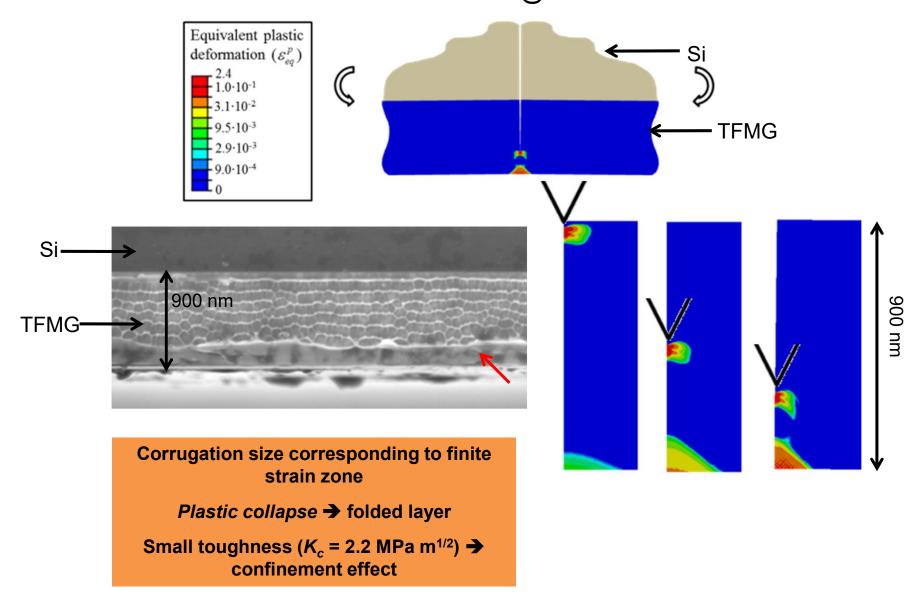
Corrugation width ↑ when thickness ↑

Corrugation size << bulk values ~ mm (Xi et al. PRL 2005)

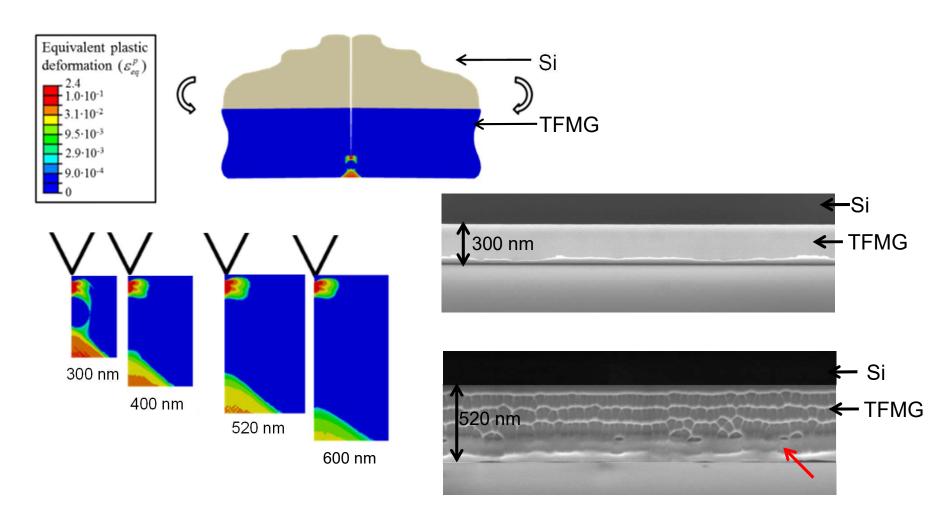
Fracture toughness (2 to 4 MPa m^{1/2} << bulk values ($K_c \sim 50$ MPa m^{1/2})



Finite element simulations of static crack @ 900 nm film







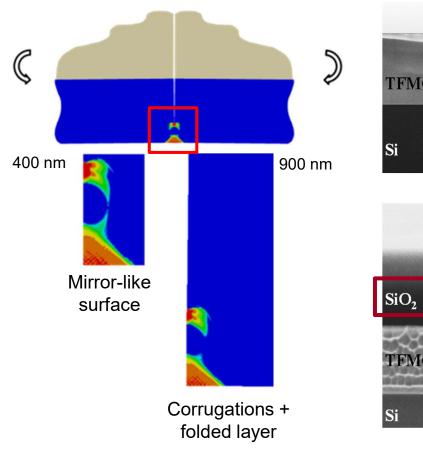
Plastic collapse for 300 and 400 nm-thick film

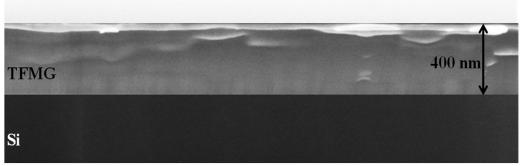
→ mirror-like surface

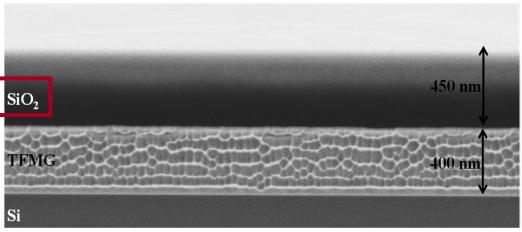
M. Ghidelli et al., Acta Materialia (2015)



Is it possible to avoid the *plastic collapse* for thicknesses < 500 nm? Add a cap layer







Compressive plastic zone shifting into the SiO₂ layer and no folded layer

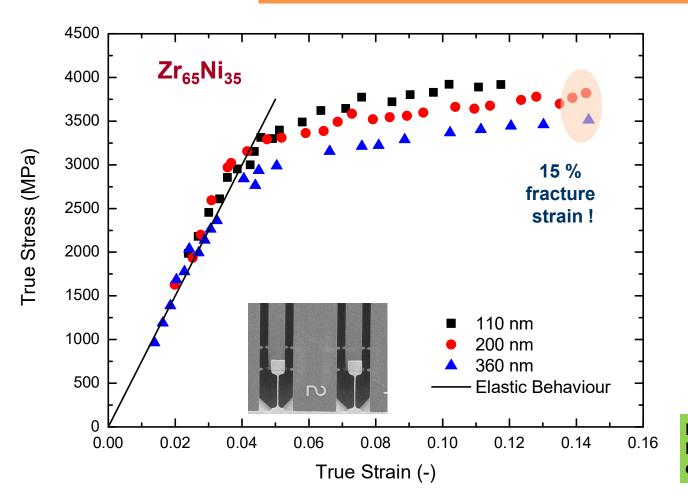
M. Ghidelli et al., Acta Materialia (2015)



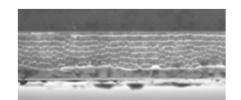
Ultra-tough metallic glasses

with UCL on-chip

Metallic glasses are wonderful materials except for their brittleness



Can we learn from this discovery to make ductile-tough metallic glasses?



Ph. D. thesis M. Ghidelli, 2015 INPG + UCL e.g. Ghidelli et al., Acta Mater 2015



Outline

1. Introduction

2. Fracture of films on substrates

- test methods and extraction of G
- example 1 : CrN on polymer (indentation)
- example 2 : SiN on polymer (subcritical crack growth)
- example 3 : Au on polymer (for flexible electronics)

3. Fracture of freestanding films

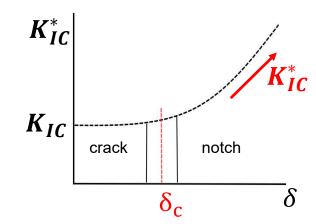
- Test methods for measuring the fracture strength strain
- fracture strength of brittle films
- fracture strain of ductile films
- fracture toughness

How to characterize the fracture resistance of thin freestanding films?

Freestanding configurations - challenges

 Initial crack tip opening displacement must be smaller than the critical crack tip opening displacement for valid fracture mechanics test

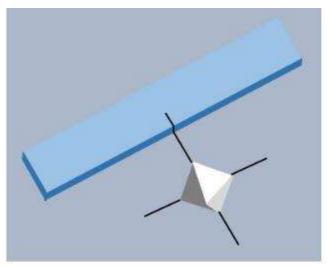
$$\delta_c \approx \frac{G_c}{\sigma_0}$$
 for $G_c = 1 \text{J/m}^2 \& \sigma_0 = 5 \text{ GPa}, \, \delta_c \approx 0.2 \text{ nm}$ for $G_c = 10 \text{J/m}^2 \& \sigma_0 = 0.2 \text{ GPa}, \, \delta_c \approx 50 \text{ nm}$



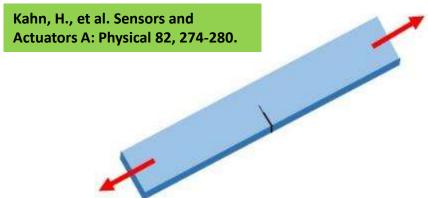
- Transfer of films without damaging
- Clamping
- Detecting cracking initiation and crack growth
- Measure extremely small loads
- Generate statistically representative data

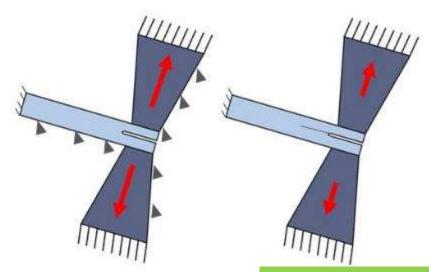


Two methods with valid cracks



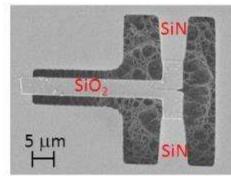
 pre-crack by nanoindentation, release, pull in tension with microdevice, determine cracking initiation

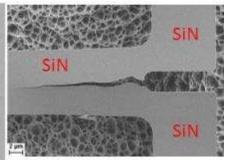




S. Jaddi et al. JMPS 2019

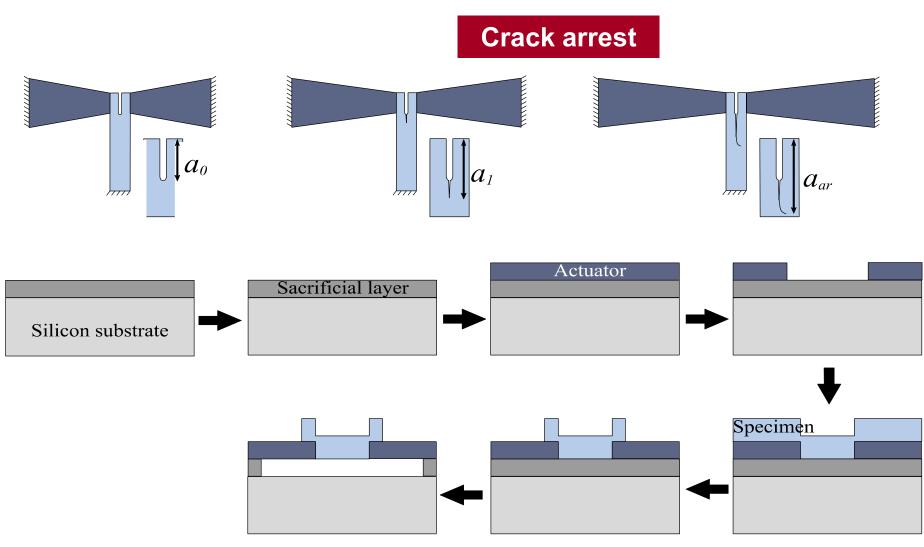
(2) notched specimen, internal stressed actuator, release, cracking and arrest, measure final crack length







Extension to crack on chip configuration



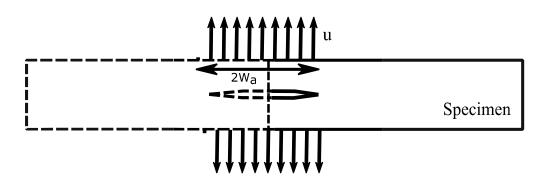


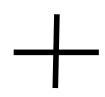
Theoretical analysis

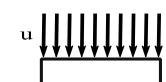
Actuator

$$\frac{2u}{F} = C(E, a, W_a, W, L)$$

$$u = \frac{L_a}{E_a} \left(\sigma_a^{int} (1 - v_a) - \frac{F}{t_a W_a^*} \right)$$







Actuator

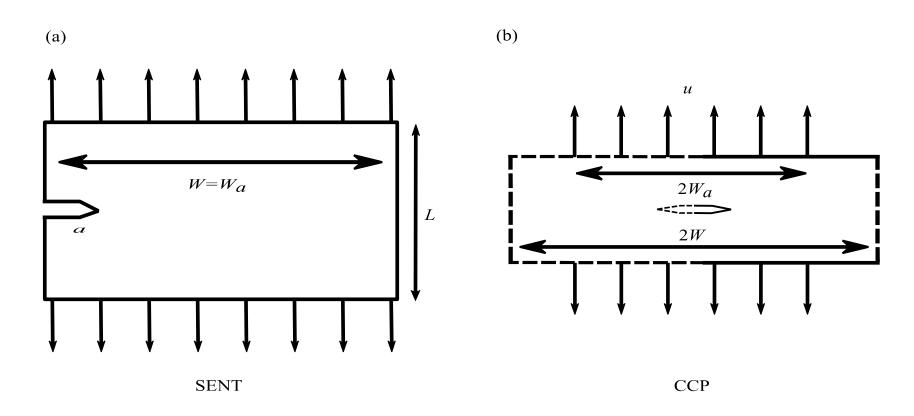
Assuming linear elastic overall behaviour, use superposition principle

$$F = \left(\frac{(1 - v_a)L_a}{\frac{L_a}{t_a W_a^*} + \frac{E_a}{E}} \frac{C^* \left(a, \frac{W_a}{W}, \frac{L}{W}\right)}{2}\right) \sigma_a^{int}$$



Theoretical analysis

With short crack length, the test structures ressemble Center Cracked Panels (CCP) or Single Edge Notched Tension (SENT)



Limit 1: $L \approx W \& L < W_a$



Theoretical analysis SENT and CCP panels

$$K = \frac{F}{W^*t} Y\left(\frac{a}{W}\right) \sqrt{\pi a}$$

with
$$G = \frac{F^2}{2t} \frac{\partial C}{\partial a}$$
 and $G = \frac{K^2}{E^*}$

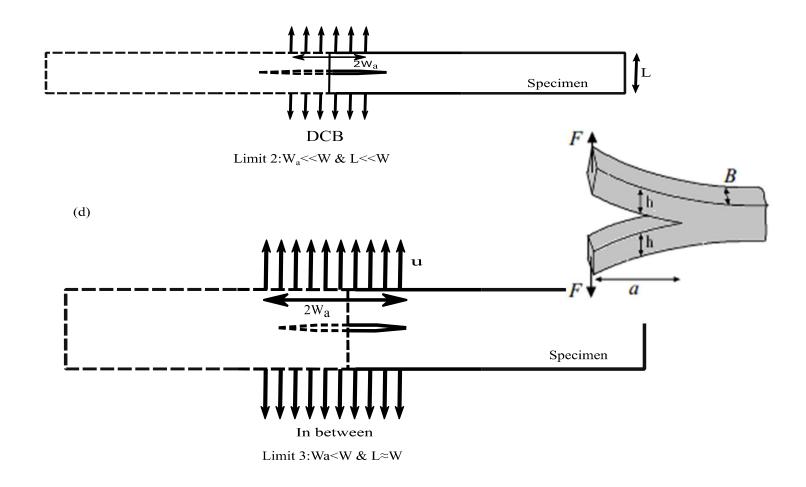
$$K_{SENTapprox} = \frac{(1 - v_a)\sigma_a^{int}\sqrt{L_a}}{L} \sqrt{\frac{L_a}{L} \frac{1.12\sqrt{\pi \frac{a}{w^*}}\sqrt{\frac{W^*}{L}}}{\frac{L_a}{W_a} \frac{t}{t_a} + \frac{E_a}{2E} \left(\alpha_2 1.12^2 \pi \left(\frac{a}{W^*}\right)^2 \frac{W^*}{L} + \alpha_3\right)}}$$

$$K_{CCPapprox} = (1 - \nu_a)\sigma_a^{int}\sqrt{L_a}\sqrt{\frac{L_a}{L}}\frac{\sqrt{\pi \frac{a}{w^*}}\sqrt{\frac{W^*}{L}}}{\frac{L_a}{L}\frac{W}{W_a}\frac{t}{t_a} + \frac{E_a}{2E}\left(\alpha_2\pi\left(\frac{a}{W^*}\right)^2\frac{W^*}{L} + \alpha_3\right)}$$



Theoretical analysis

With longer crack lengths, the test structures ressemble Double Cantilever Beam geometry (DCB)





Theoretical analysis

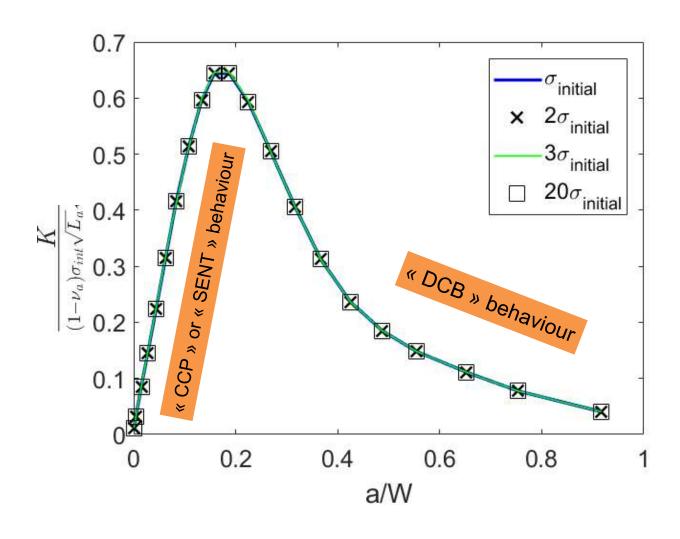
with
$$G = \frac{F^2}{2t} \frac{\partial C}{\partial a}$$
 and $G = \frac{K^2}{E^*}$

$$K_{DCBasym} = 4\sqrt{\frac{6}{\alpha_2}} (1 - \nu_a) \sigma_a^{int} \sqrt{L_a} \frac{\frac{a L^2}{WW^2} \sqrt{\frac{L_a}{L}}}{4 \frac{E_a a^3}{E W^3} + \frac{L^3 L_a t}{W^3 W_a^* t_a}}$$

$$K_{DCBsym} = 2\sqrt{\frac{6}{\alpha_2}} (1 - \nu_a) \sigma_a^{int} \sqrt{L_a} \frac{\frac{a L^2}{WW^2} \sqrt{\frac{L_a}{L}}}{4\frac{E_a a^3}{E W^3} + \frac{L^3 L_a t}{W^3 W_a^* t_a}}$$

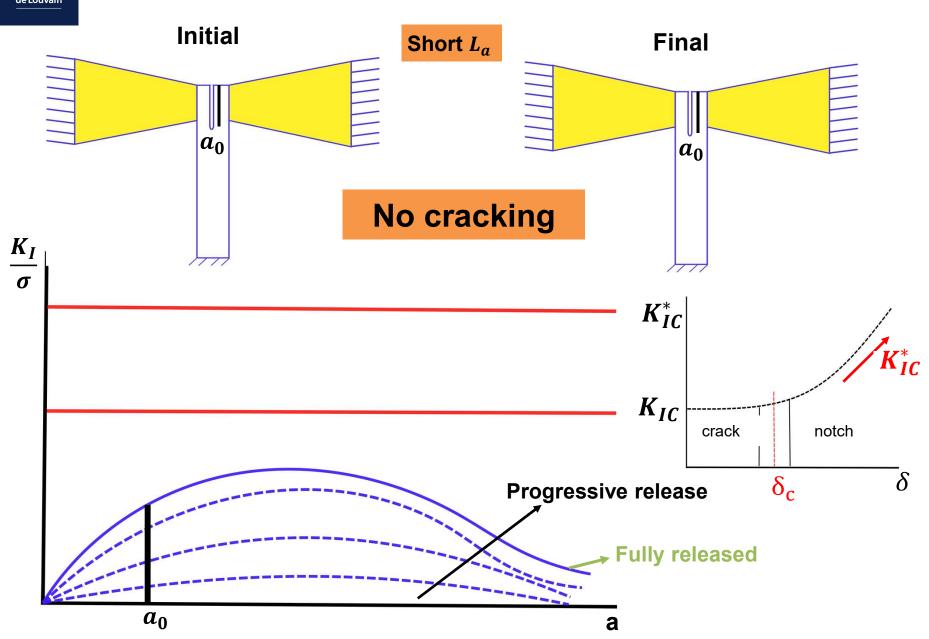
Finite element analysis

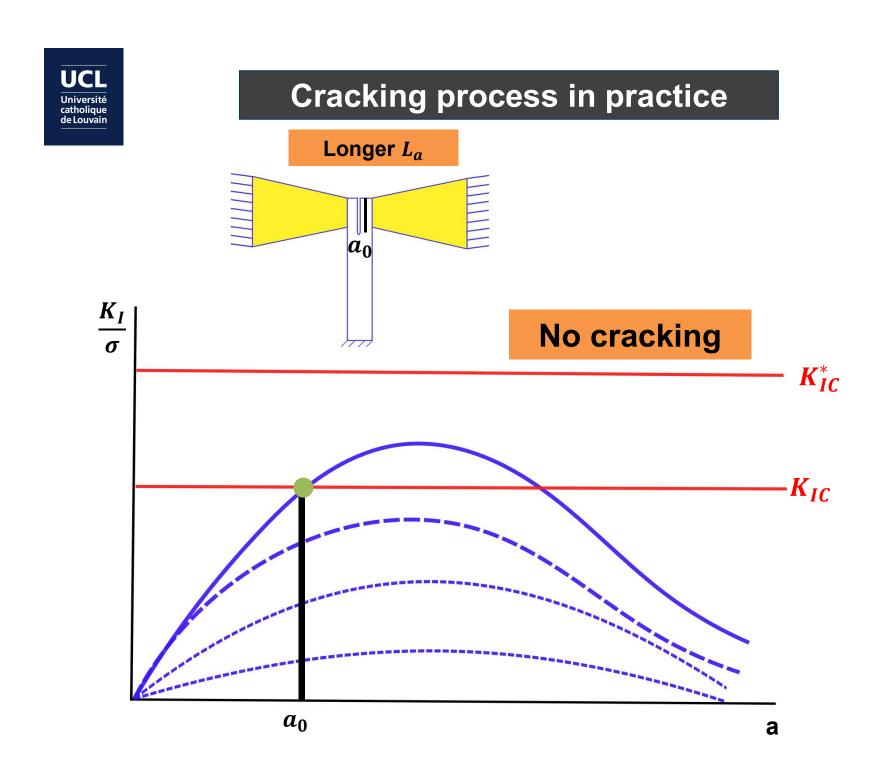
Verification : K_l scales linearly with internal stress in actuator

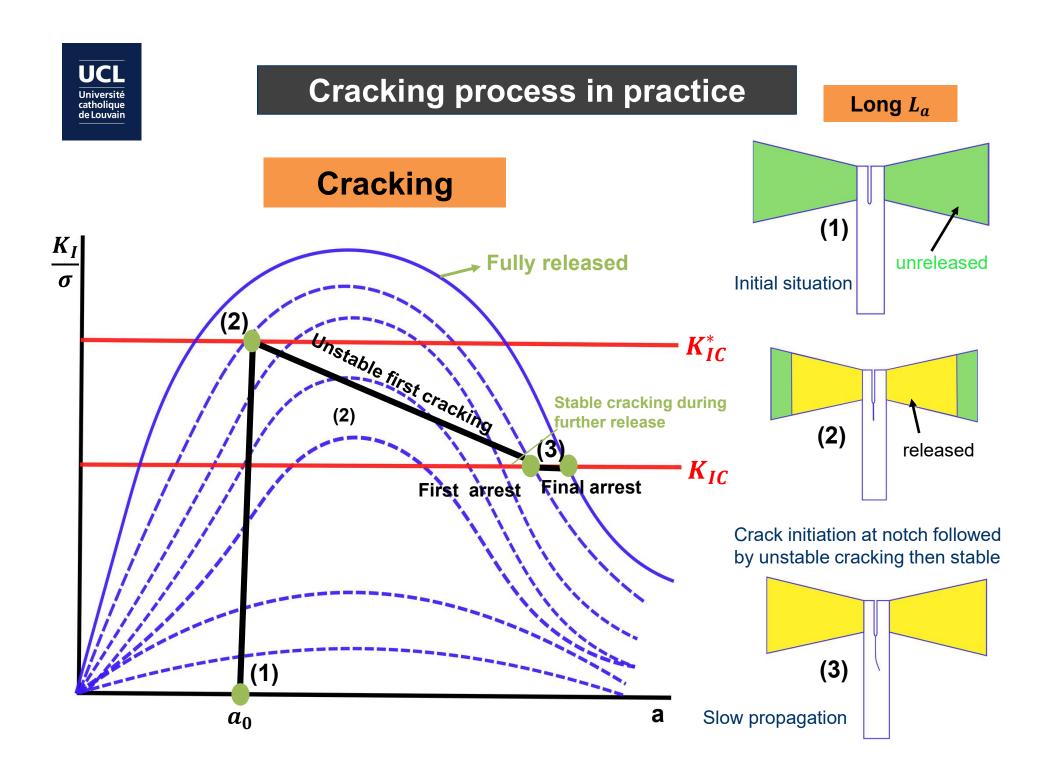




Cracking process in practice



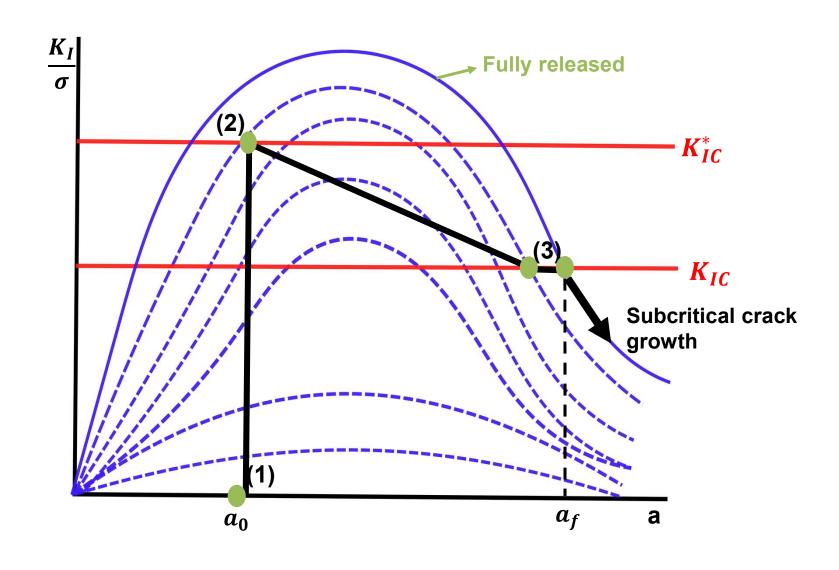






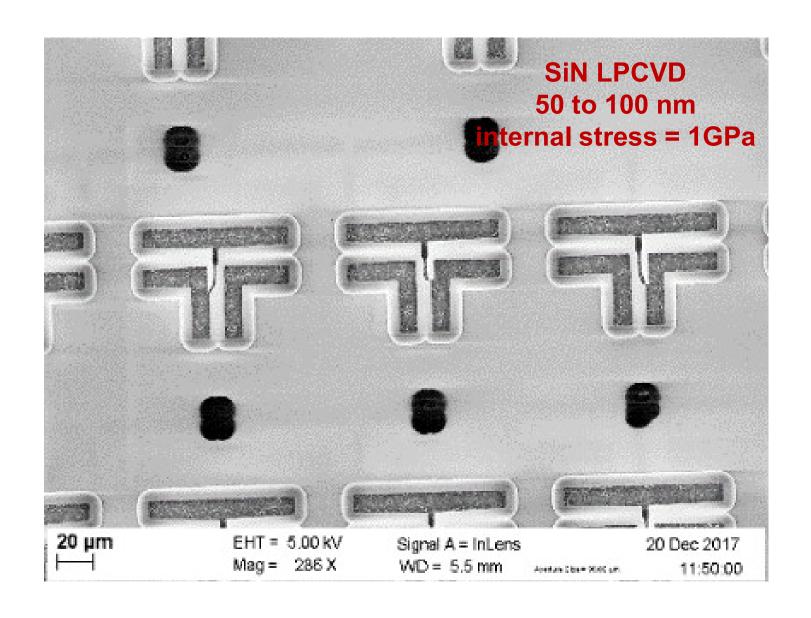
Cracking process in practice

Possible subcritical crack growth: environmental, creep...





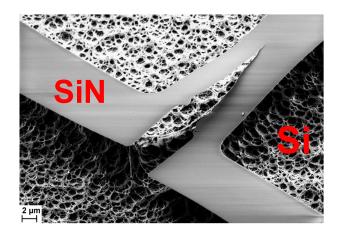
Experimental results



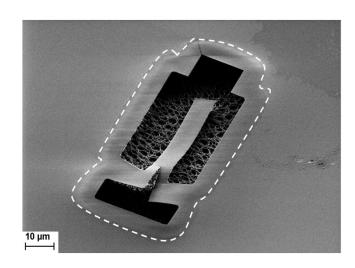


Experimental problems

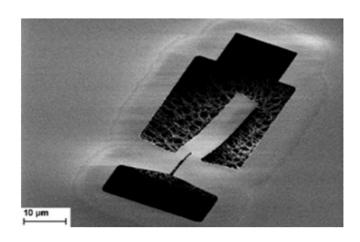
Mode III



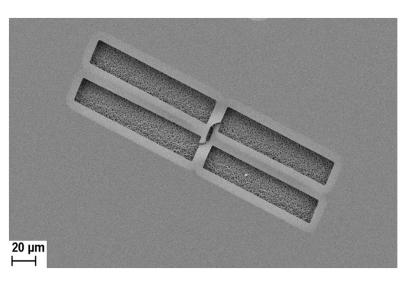
Underetching



Stiction



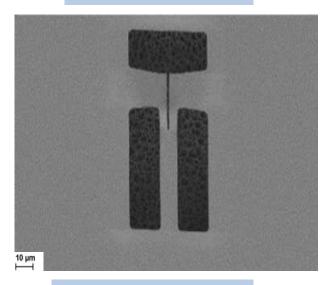
Kinking out



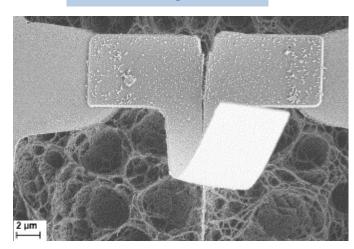


Experimental problems

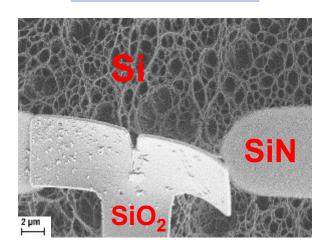
No cracking



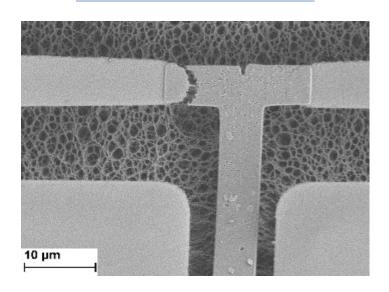
Out of plane



No attachment

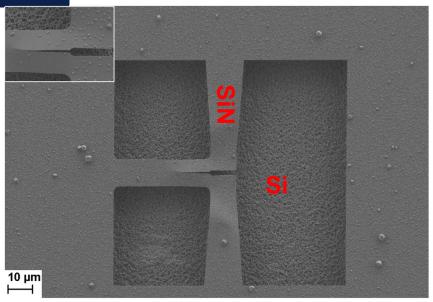


Undesired fracture

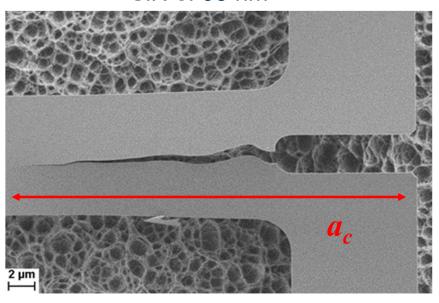




SiN of 55 nm

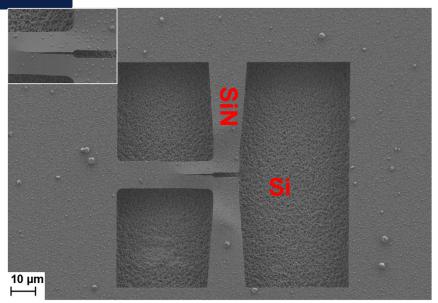


SiN of 93 nm

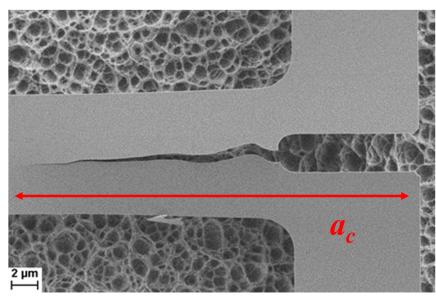




SiN of 55 nm



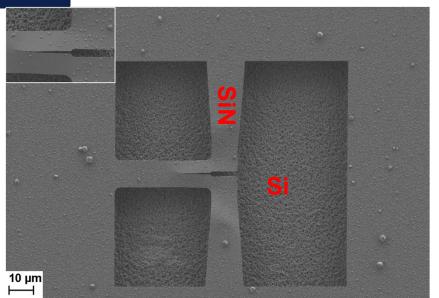
SiN of 93 nm



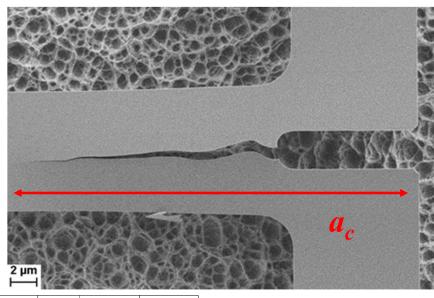




SiN of 55 nm







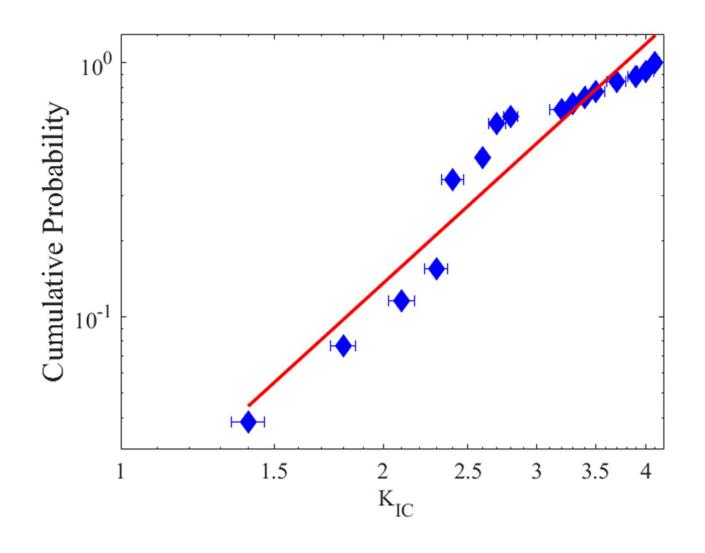


Ref.	L_a^*	L	W	W_a^*	$t=t_a$	a_{c_arrest}	K_{Ic}
number	[µm]	[µm]	[µm]	[µm]	[nm]	[µm]	[MPa√m]
I	15±1	10±1	50±2	11 ±0.2	55±1	25.5 ±0.2	1.2±0.1
II	10±1	10±1	30±2	11 ±0.2	55±1	19±0.2	1.4±0.2
III	10±0.3	8±0.1	50±1	9±0.1	55 ±1	14.5±0.7	1.8±0.1
IV	85±4	8.8±1	48±3	10.25 ±0.3	93 ±1	26.9±0.1	1.7±0.3
V	62.4±4	8.8 ± 1	48.3±2	10.05 ±0.3	93 ±1	27±0.2	1.4±0.2
VI	75.5 ± 2	9.1 ±1	48.5±1	10.25 ±0.1	93 ±1	27.7±0.1	1.5±0.2
VII	85.9±4	9±1	48.2±4	10.25 ±0.3	93 ±1	28.2 ±0.1	1.6±0.3
VIII	53±5	8.6±1.5	48.5±3	10.6 ±0.7	93 ±1	18±1	2.9 ±0.1
IX	50±6	8.6±1.5	48±3	10.5 ±0.3	93 ±1	20±1.2	2.1±0.3
X	53.5±5	9.4±1	48±1	9.8±0.3	93 ±1	24.4±0.2	1.6±0.2
XI	46.1±1	9±1	44±1	9.5±0.4	93 ±1	23 ±0.2	1.5±0.2
XII	65.2 ± 7	9±1	35±1	9.6±0.5	93 ±1	16.5±0.3	3.4±0.4
XIII	54±2	9±1	37±2	9.55 ±0.3	93 ±1	17.2±0.4	2.9±0.3
XIV	52.7±4	9±1	42±2	10.3 ±0.3	93 ±1	20.7±0.2	2.1±0.4
XV	62.5±2	9±1	39.2±1	10.3 ±0.5	93 ±1	21±1.5	2.4±0.05
	$K_{Ic_mean}{\sim}~2$ MPa \sqrt{m}						

 K_c of 1.82 \pm 0.03 MPa.m^{1/2}

Pierron Group (2016) ACS Appl. Mater. Interfaces

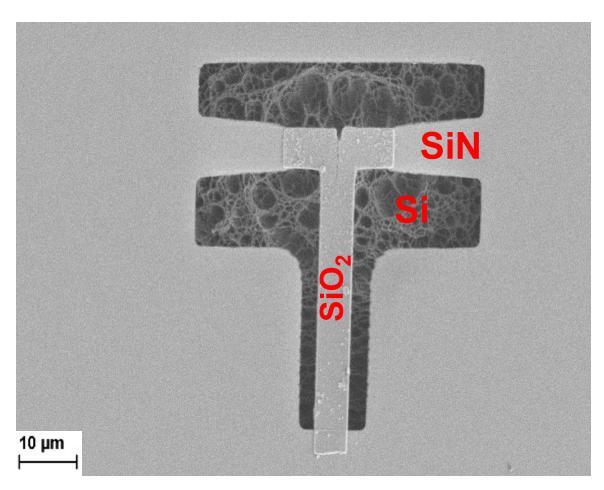


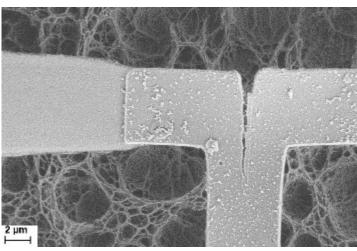


Median= 2.7 MPa \sqrt{m} $R^2 = 92\%$ Mean=2.9 MPa \sqrt{m}



Application to 150 nm thick SiO₂







Approach 2 : Freestanding thin films Conclusion

Pro and cons

Generate true intrinsic properties (but ...) – no artifact from substrate

Allow in situ TEM testing

Testing is complex – MEMS types devices help

Points of attention

- Importance of the state of the surface (oxide, roughness, ...)
- Higher strength at small scale but also higher rate sensitivity
- Huge effect of imperfections: statistical treatment essential
- Fracture toughness often not valid except if sufficiently brittle



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- test methods and extraction of G
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- example 2 : SiN on polymer (subcritical crack growth)
- example 3 : Au on polymer (for flexible electronics)

3. Fracture of freestanding films

- Test methods for measuring the fracture strength & strain
- fracture strength of brittle films
- fracture strain of ductile films
- fracture toughness